

UCC12050 高效、低 EMI、5kV_{RMS} Reinforced 隔离式直流/直流转换器

1 特性

- 采用集成变压器技术的高效直流/直流转换器
- 符合 CISPR32 B 级 EMI 标准限制，在双层 PCB 的整个负载范围内没有铁氧体磁珠
- 稳健可靠的隔离栅：
 - 隔离额定值：5kV_{RMS}
 - 浪涌能力：10kV_{PK}
 - 工作电压：1.2kV_{RMS}
 - CMTI（典型值）：±100V/ns
- 功率输出（典型值）：500mW
- 5.0V 或 3.3V 稳压输出，具有可选的 400mV 净空电压为 LDO 供电
- 输入电压：4.5V 至 5.5V
- 短路恢复
- 热关断保护
- 16 引脚宽体 SOIC 封装，爬电距离和间隙大于 8mm
- 工作温度范围：-40°C 至 125°C
- 计划的安全相关认证：
 - 符合 DIN V VDE V 0884-11:2017-01 标准的 7071V_{PK} 增强型隔离
 - 符合 UL 1577 标准且长达 1 分钟的 5000V_{RMS} 隔离
 - 获得 CSA 认证，符合 IEC 60950-1、IEC 62368-1 和 IEC 60601-1 终端设备标准
 - 符合 GB4943.1-2011 的 CQC 认证

2 应用

- PLC 模拟输入和输出模块
- 隔离式电压和电流感应
- 保护继电器和智能断路器
- RS-485/RS-422/CAN 收发器
- 患者监护
- 隔离式通信模块

3 说明

UCC12050 是一款具有 5kV_{RMS} reinforced 隔离额定值的直流/直流转换器，旨在为需要偏置电源及稳压输出电压的隔离电路提供有效的隔离电源。该器件集成了具有专有架构的变压器和直流/直流控制器，可提供 500mW（典型值）的隔离功率，并具有较高的效率和低 EMI。

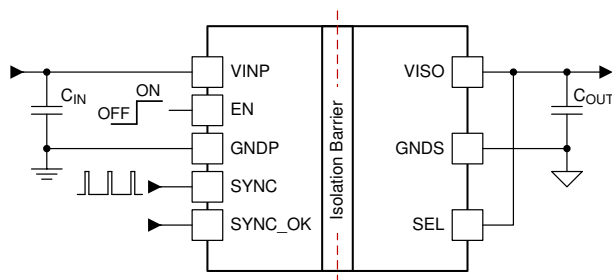
UCC12050 集成了保护功能，提高了系统的稳健性。该器件还具有使能引脚、同步功能以及 5V 或 3.3V 稳压输出选项（带净空电压）。UCC12050 是一种薄型、小型化解决方案，采用高度为 2.65mm（典型值）的宽体 SOIC 封装。

器件信息⁽¹⁾

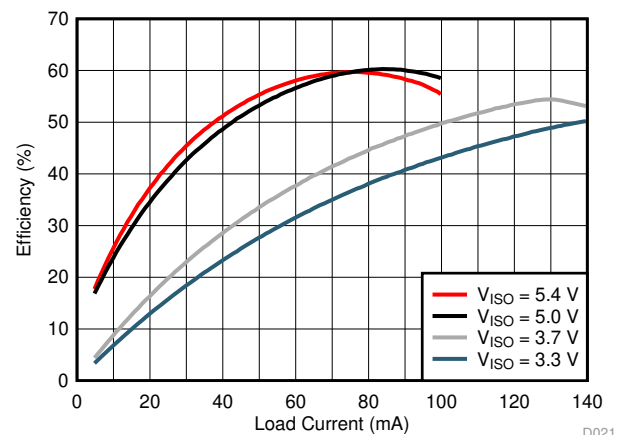
器件型号	封装	封装尺寸（标称值）
UCC12050	DVE SOIC (16)	10.30mm × 7.50mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

简化应用



典型效率与负载间的关系



V_{INP} = 5.0V

T_A = 25°C

D021



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4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision B (December 2019) to Revision C	Page
• 已添加 在整个文档中添加了更新文本	1
• Added footnote to Insulation Specifications table	5

Changes from Revision A (September 2019) to Revision B	Page
• 已更改 将销售状态从“预告信息”更改为“初始发行版”	1

5 Pin Configuration and Functions

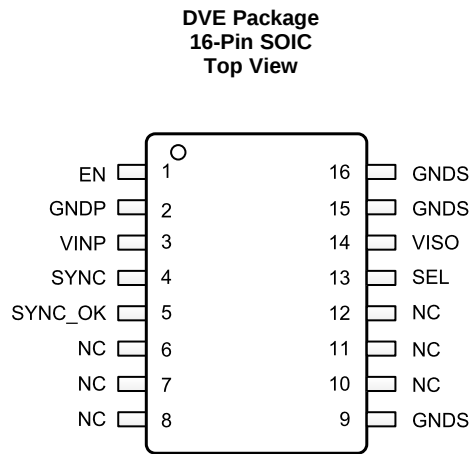


Table 1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
EN	1	I	Enable pin. Forcing EN low disables the device. Pull high to enable normal device functionality.
GNDP	2	P	Power ground return connection for VINP.
GNDP	9	P	Connect to GNDP plane on printed circuit board. Do not use as only ground connection for VISO. Ensure pin 15 is connected to circuit ground.
	16		
GNDP	15	P	Secondary side ground return connection for VISO. Connect bypass capacitor from VISO to this pin.
NC	6	—	Pins internally connected together. No other electrical connection. Pins belong to primary-side voltage domain. Connect to GNDP on printed circuit board.
	7		
	8		
	10	—	No internal connection. Pin belongs to isolated voltage domain. Connect to GNDP on printed circuit board.
	11		
	12		
SYNC	4	I	Synchronous clock input pin. Provide a clock signal to synchronize multiple UCC12050 devices or connect to GNDP for standalone operation using the internal oscillator. If the SYNC pin is left open make sure to separate it from any switching noise to avoid false clock coupling.
SYNC_OK	5	O	Active-low, open-drain diagnostic output. Pin is asserted LOW if there is no external SYNC clock or one that is outside of the operating range of the UCC12050 is detected. In this state, the external clock is ignored and the DC-DC converter is clocked by the internal oscillator. The pin is in high-impedance if a clock is applied on SYNC.
SEL	13	I	V _{ISO} selection pin. V _{ISO} setpoint is 5.0 V when SEL is shorted to V _{ISO} , 5.4 V when SEL is connected to V _{ISO} through a 100-kΩ resistor, 3.3 V when SEL is shorted to GNDP, and 3.7 V when SEL is connected to GNDP through a 100-kΩ resistor. For more information see the Device Functional Modes section.
VINP	3	P	Primary side input supply voltage pin. A 10-μF ceramic capacitor to GNDP on pin 2, placed close to the device pins, is required.
VISO	14	P	Isolated supply voltage pin. A 10-μF ceramic capacitor to GNDP on pin 15, placed close to the device pins, is required. See VISO Output Capacitor Selection section.

(1) P = Power, G = Ground, I = Input, O = Output

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

	MIN	MAX	UNIT
V _{INP} to GNDP	−0.3	6.0	V
EN, SYNC, SYNC_OK, to GNDP	−0.3	V _{INP} + 0.3, ≤ 6.0	V
V _{ISO} to GNDS	−0.3	6.0	V
SEL to GNDS	−0.3	V _{ISO} + 0.3, ≤ 6.0	V
V _{ISO} output power at T _a = 25°C, P _{OUT_MAX} ⁽²⁾		675	mW
Operating junction temperature range, T _J	−40	150	°C
Storage temperature, T _{stg}	−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) See the [V_{ISO} Load Recommended Operating Area](#) section for maximum rated values across temperature and V_{INP} conditions for each different V_{ISO} output mode.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±1000
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±500

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{INP}	Primary side supply voltage	4.5	5.0	5.5	V
V _{EN}	EN pin input voltage	0		5.5	V
V _{SYNC}	SYNC pin input voltage	0		5.5	V
V _{SYNC-OK}	SYNC_OK pin drain pin voltage	0		5.5	V
V _{ISO}	Isolated power supply voltage	0		5.7	V
V _{SEL}	Input voltage	0		5.7	V
f _{SYNC}	External DC-DC converter synchronization signal frequency	14.4	16.0	17.6	MHz
P _{VISO}	V _{ISO} output power at T _a = 25°C ⁽¹⁾			500	mW
T _a	Ambient temperature	−40		125	°C
T _J	Junction temperature	−40		150	°C

- (1) See the [V_{ISO} Load Recommended Operating Area](#) section for maximum rated values across temperature and V_{INP} conditions for each different V_{ISO} output mode.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		UCC12050	UNIT
		DVE (SOIC)	
		16 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	63.8	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	21.4	°C/W
R _{θJB}	Junction-to-board thermal resistance	38.5	°C/W
ψ _{JT}	Junction-to-top characterization parameter	10.2	°C/W
ψ _{JB}	Junction-to-board characterization parameter	37.2	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	—	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Power Ratings

 $V_{INP} = 5.0V$, $C_{INP} = C_{OUT} = 10 \mu F$, $T_J = 150^\circ C$, Internal Clock mode

PARAMETER		TEST CONDITIONS	VALUE	UNIT
P_D	Power dissipation	SEL connected to GNDS (3.3-V V_{ISO} output mode), $I_{ISO} = 135 \text{ mA}$	460	mW
P_{DP}	Power dissipation by driver side (primary)		148	mW
P_{DS}	Power dissipation by rectifier side (secondary)		164	mW
P_{DT}	Power dissipation by transformer		148	mW

6.6 Insulation Specifications

PARAMETER		TEST CONDITIONS	VALUE	UNIT
GENERAL				
CLR	External clearance ⁽¹⁾	Shortest terminal-to-terminal distance through air	> 8	mm
CPG	External creepage ⁽¹⁾	Shortest terminal-to-terminal distance across the package surface	> 8	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance)	> 120	μm
CTI	Comparative tracking index	DIN EN 60112 (VDE 0303-11); IEC 60112	> 600	V
	Material group	According to IEC 60664-1	I	
	Overvoltage Category	Rated mains voltage ≤ 300 V _{RMS}	I-IV	
		Rated mains voltage ≤ 600 V _{RMS}	I-IV	
		Rated mains voltage ≤ 1000 V _{RMS}	I-III	
DIN V VDE V 0884-11:2017-01 ⁽²⁾ (Planned Certification Targets)				
V _{IORM}	Maximum repetitive peak isolation voltage	AC voltage (bipolar)	1414	V _{PK}
V _{IOWM}	Maximum working isolation voltage	AC voltage (sine wave) Time dependent dielectric breakdown (TDDB) test	1000	V _{RMS}
		DC voltage	1414	V _{DC}
V _{IOTM}	Maximum transient isolation voltage	V _{TEST} = V _{IOTM} , t = 60s (qualification); V _{TEST} = 1.2 × V _{IOTM} , t = 1s (100% production)	7071	V _{PK}
V _{IOSM}	Maximum surge isolation voltage ⁽³⁾	Test method per IEC 62368-1, 1.2/50 μs waveform, V _{TEST} = 1.6 × V _{IOSM} = 10000 V _{PK} (qualification)	6250	V _{PK}
q _{pd}	Apparent charge ⁽⁴⁾	Method a: After I/O safety test subgroup 2/3, V _{ini} = V _{IOTM} , t _{ini} = 60 s; V _{pd(m)} = 1.2 × V _{IORM} = 1696 V _{PK} , t _m = 10 s	≤ 5	pC
		Method a: After environmental tests subgroup 1, V _{ini} = V _{IOTM} , t _{ini} = 60 s; V _{pd(m)} = 1.6 × V _{IORM} = 2262 V _{PK} , t _m = 10 s	≤ 5	
		Method b1: At routine test (100% production) and preconditioning (type test) V _{ini} = 1.2 × V _{IOTM} , t _{ini} = 1 s; V _{pd(m)} = 1.875 × V _{IORM} = 2651 V _{PK} , t _m = 1 s	≤ 5	
C _{IO}	Barrier capacitance, input to output ⁽⁵⁾	V _{IO} = 0.4 sin (2πft), f = 1 MHz	~3.5	pF
R _{IO}	Isolation resistance, input to output ⁽⁵⁾	V _{IO} = 500 V, T _A = 25°C	> 10 ¹²	Ω
		V _{IO} = 500 V, 100°C ≤ T _A ≤ 125°C	> 10 ¹¹	
		V _{IO} = 500 V at T _S = 150°C	> 10 ⁹	
	Pollution degree		2	
	Climatic category		40/125/21	
UL 1577 (Planned Certification Target)				
V _{ISO}	Withstand isolation voltage	V _{TEST} = V _{ISO} = 5000 V _{RMS} , t = 60 s (qualification); V _{TEST} = 1.2 × V _{ISO} = 6000 V _{RMS} , t = 1 s (100% production)	5000	V _{RMS}

- Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance. Creepage and clearance on a printed-circuit board become equal in certain cases. Techniques such as inserting grooves and/or ribs on a printed circuit board are used to help increase these specifications.
- This coupler is suitable for *safe electrical insulation* only within the maximum operating ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.
- Testing is carried out in air or oil to determine the intrinsic surge immunity of the isolation barrier.
- Apparent charge is electrical discharge caused by a partial discharge (pd).
- All pins on each side of the barrier tied together creating a two-terminal device

6.7 Safety-Related Certifications

VDE	CSA	UL	CQC	TUV
Plan to certify according to DIN V VDE V 0884-11:2017-01	Plan to certify according to IEC 60950-1, IEC 62368-1, and IEC 60601-1	Plan to certify under UL 1577 Component Recognition Program	Plan to certify according to GB4943.1-2011	Plan to certify according to EN 61010-1:2010 (3rd Ed) and EN 60950-1:2006/A11:2009/A1:2010/A12:2011/A2:2013
Reinforced insulation Maximum transient isolation voltage, 7071 V _{PK} ; Maximum repetitive peak isolation voltage, 1414 V _{PK} ; Maximum surge isolation voltage, 6250 VPK	Reinforced insulation per CSA 60950-1-07+A1+A2, IEC 60950-1 2nd Ed. +A1+A2, CSA 62368-1-14 and IEC 62368-1 2nd Ed., 800 V _{RMS} maximum working voltage (pollution degree 2, material group I) ; 2 MOPP (Means of Patient Protection) per CSA 60601-1:14 and IEC 60601-1 Ed.3+A1, 250 V _{RMS} maximum working voltage	Single protection, 5000 V _{RMS}	Reinforced insulation, Altitude ≤ 5000 m, Tropical Climate, 700 V _{RMS} maximum working voltage	5000 V _{RMS} Reinforced insulation per EN 61010-1:2010 (3rd Ed) up to working voltage of 600 V _{RMS} 5000 V _{RMS} Reinforced insulation per EN 60950-1:2006/A11:2009/A1:2010/A12:2011/A2:2013 up to working voltage of 800 V _{RMS}
Certificate number: (planned)	Master contract number: (planned)	File number: (planned)	Certificate number: (planned)	Client ID number: (planned)

6.8 Safety Limiting Values

Safety limiting intends to minimize potential damage to the isolation barrier upon failure of input or output circuitry.

PARAMETER		TEST CONDITIONS	MAX	UNIT
I _S	Safety input current ⁽¹⁾	R _{θJA} = 63.8°C/W, V _I = 5.5 V, T _J = 150°C, T _A = 25°C	356	mA
		R _{θJA} = 63.8°C/W, V _I = 4.5 V, T _J = 150°C, T _A = 25°C	435	
P _S	Safety input power	R _{θJA} = 63.8°C/W, T _J = 150°C, T _A = 25°C	1960	mW
T _S	Safety temperature ⁽¹⁾		150	°C

- (1) The maximum safety temperature, T_S, has the same value as the maximum junction temperature, T_J, specified for the device. The I_S and P_S parameters represent the safety current and safety power respectively. The maximum limits of I_S and P_S should not be exceeded. These limits vary with the ambient temperature, T_A. The junction-to-air thermal resistance, R_{θJA}, in the [Thermal Information](#) table is that of a device installed on a high-K test board for leaded surface-mount packages. Use these equations to calculate the value for each parameter: T_J = T_A + R_{θJA} × P, where P is the power dissipated in the device. T_{J(max)} = T_S = T_A + R_{θJA} × P_S, where T_{J(max)} is the maximum allowed junction temperature. P_S = I_S × V_I, where V_I is the maximum input voltage.

6.9 Electrical Characteristics

Over operating temperature range ($T_J = -40^{\circ}\text{C}$ to 150°C), $V_{\text{INP}} = 4.5\text{V}$ to 5.5V , $C_{\text{INP}} = C_{\text{OUT}} = 10\text{ }\mu\text{F}$, SEL connected to V_{ISO} , unless otherwise noted. All typical values at $T_J = 25^{\circ}\text{C}$ and $V_{\text{INP}} = 5.0\text{V}$.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
INPUT SUPPLY						
I_{VINQ}	VINP quiescent current, disabled	EN=LOW			100	μA
I_{VINO}	VINP operating current, no load	EN=HI; SEL shorted to VISO (5.0V output)		50		mA
		EN=HI; SEL 100k Ω to VISO (5.4V output)		45		
		EN=HI; SEL shorted to GNDS (3.3V output)		90		
		EN=HI; SEL 100k Ω to GNDS (3.7V output)		80		
$I_{\text{VIN_SC}}$	DC current from VINP supply under short circuit on VISO	VISO short to GNDS		245		mA
V_{UVPR}	VINP under-voltage lockout rising threshold			4.2		V
V_{UVPF}	VINP under-voltage lockout falling threshold			3.7		V
V_{UVPH}	VINP under-voltage lockout hysteresis			0.5		V
EN, SYNC INPUT PINS						
V_{IR}	Input voltage threshold, logic HIGH	Rising edge			2.2	V
V_{IF}	Input voltage threshold, logic LOW	Falling edge	0.8			V
I_{EN}	Enable Pin Input Current	$V_{\text{EN}} = 5.0\text{ V}$		5	10	μA
I_{SYNC}	SYNC Pin Input Current	$V_{\text{SYNC}} = 5.0\text{ V}$		0.02	1	μA
SYNC_OK PIN						
V_{OL}	SYNC_OK output low voltage	$I_{\text{SYNC_OK}} = -2\text{ mA}$		0.15		V
$I_{\text{LKG_SYNC_OK}}$	SYNC_OK pin leakage current	$V_{\text{SYNC_OK}} = 5.0\text{ V}$			1	μA
DC-DC CONVERTER						
V_{ISO}	Isolated supply output voltage	SEL shorted to VISO (5.0V output); $I_{\text{ISO}} = 55\text{ mA}$ ⁽¹⁾	4.7	5	5.3	V
		SEL 100k Ω to VISO (5.4 V output); $I_{\text{ISO}} = 45\text{ mA}$ ⁽¹⁾	5.1	5.4	5.7	V
		SEL shorted to GNDS (3.3V output); $I_{\text{ISO}} = 100\text{ mA}$ ⁽¹⁾	3.1	3.3	3.5	V
		SEL 100k Ω to GNDS (3.7 V output); $I_{\text{ISO}} = 90\text{ mA}$ ⁽¹⁾	3.5	3.7	3.9	V
$V_{\text{ISO(RIP)}}$	Voltage ripple on isolated supply output (pk-pk)	20-MHz bandwidth, CLOAD = 10 μF 0.1 μF , SEL shorted to VISO (5.0V output); $I_{\text{ISO}} = 100\text{ mA}$		50		mV
		20-MHz bandwidth, CLOAD = 10 μF 0.1 μF , SEL 100k Ω to VISO (5.4V output); $I_{\text{ISO}} = 90\text{ mA}$		50		mV
		20-MHz bandwidth, CLOAD = 10 μF 0.1 μF , SEL shorted to GNDS (3.3V output); $I_{\text{ISO}} = 145\text{ mA}$		50		mV
		20-MHz bandwidth, CLOAD = 10 μF 0.1 μF , SEL shorted to GNDS (3.7V output); $I_{\text{ISO}} = 130\text{ mA}$		50		mV
$V_{\text{ISO(LINE)}}$	V_{ISO} DC line regulation	SEL shorted to VISO (5.0 V output); $I_{\text{ISO}} = 50\text{ mA}$, VINP = 4.5 V to 5.5 V		1%		
		SEL shorted to GNDS (3.3 V output); $I_{\text{ISO}} = 75\text{ mA}$, VINP = 4.5 V to 5.5 V		1%		

(1) See the [V_{ISO} Load Recommended Operating Area](#) section for discussion of V_{ISO} regulation across load and temperature conditions for all output voltage settings.

Electrical Characteristics (continued)

Over operating temperature range ($T_J = -40^{\circ}\text{C}$ to 150°C), $V_{\text{INP}} = 4.5\text{V}$ to 5.5V , $C_{\text{INP}} = C_{\text{OUT}} = 10\text{ }\mu\text{F}$, SEL connected to V_{ISO} , unless otherwise noted. All typical values at $T_J = 25^{\circ}\text{C}$ and $V_{\text{INP}} = 5.0\text{V}$.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{ISO(Load)}	V _{ISO} DC load regulation	SEL shorted to VISO (5.0 V output); I _{ISO} = 0 to 100 mA		1.5%		
	V _{ISO} DC load regulation	SEL shorted to GNDS (3.3 V output); I _{ISO} = 0 to 145 mA		1.5%		
EFF	Efficiency at maximum recommended load ⁽²⁾	SEL shorted to VISO (5.0 V output); I _{ISO} = 100 mA		60%		
		SEL 100kΩ to VISO (5.4V output); I _{ISO} = 90 mA		60%		
		SEL shorted to GNDS (3.3V output); I _{ISO} = 145 mA		50%		
		SEL 100kΩ to GNDS (3.7V output); I _{ISO} = 130 mA		53%		
t _{RISE}	VISO rise time, 10% - 90%	EN = change from LO to HI, SEL shorted to VISO (5.0V output); I _{ISO} = 1 mA		750		μs
		EN = change from LO to HI, SEL 100kΩ to GNDS (3.3V output); I _{ISO} = 1 mA		300		μs
THERMAL SHUTDOWN						
TSD _{THR}	Thermal shutdown threshold	Junction Temperature, Rising		165		°C
TSD _{HYST}	Thermal shutdown hysteresis	Junction Temperature, Falling		27		°C

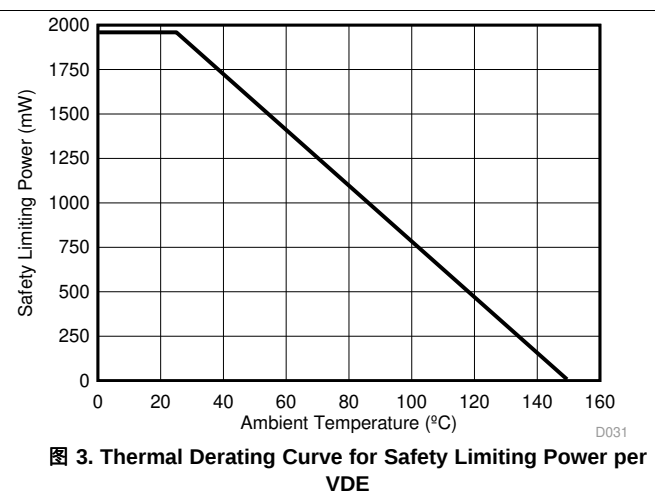
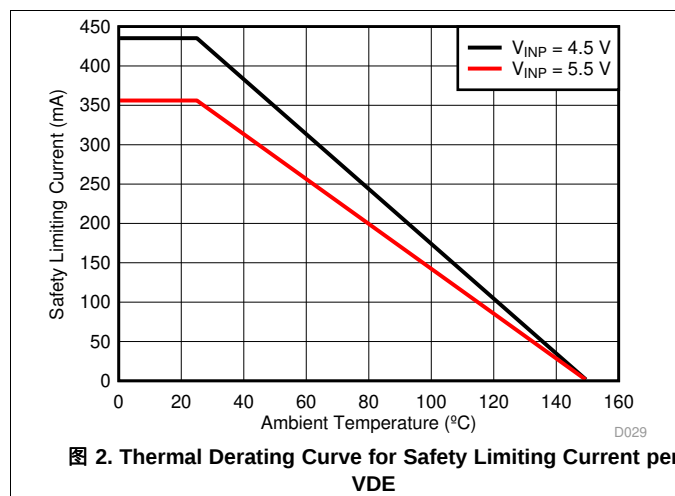
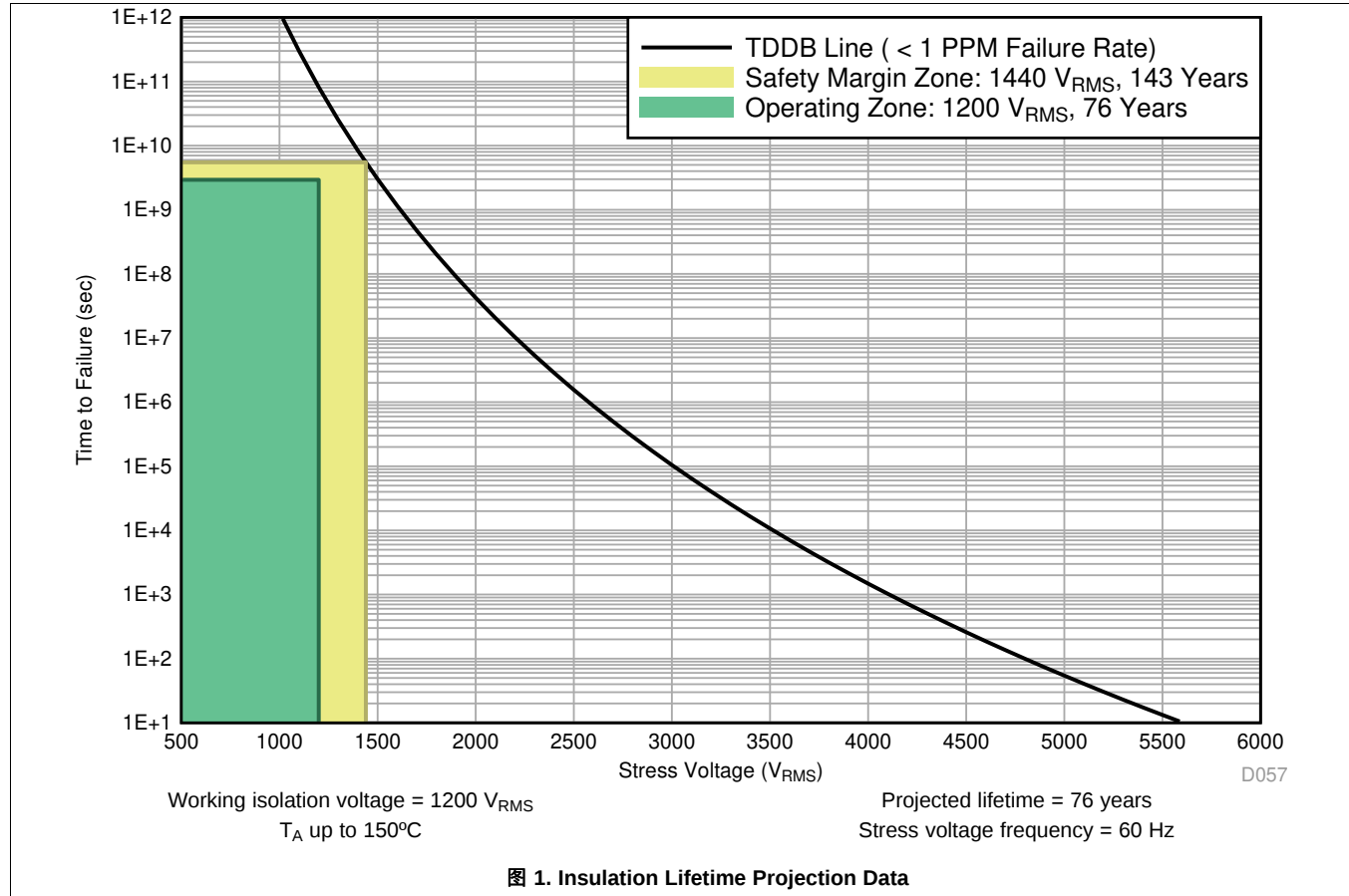
(2) Efficiency calculation: $\text{EFF} = (V_{\text{ISO}} \times I_{\text{ISO}}) / (V_{\text{INP}} \times I_{\text{INP}})$

6.10 Switching Characteristics

Over operating temperature range ($T_J = -40^{\circ}\text{C}$ to 150°C), $V_{\text{INP}} = 4.5\text{V}$ to 5.5V , $C_{\text{INP}} = C_{\text{OUT}} = 10\text{ }\mu\text{F}$, SEL connected to V_{ISO} , unless otherwise noted. All typical values at $T_J = 25^{\circ}\text{C}$ and $V_{\text{INP}} = 5.0\text{V}$.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
f_{SYNC}	DC-DC Converter Clock	Internal clock mode	7.2	8	8.8	MHz
CMTI	Static common-mode transient immunity	Slew Rate of GNDP versus GNDS, $V_{\text{CM}} = 1000\text{ V}$		100		V/ns

6.11 Insulation Characteristics Curves



6.12 Typical Characteristics

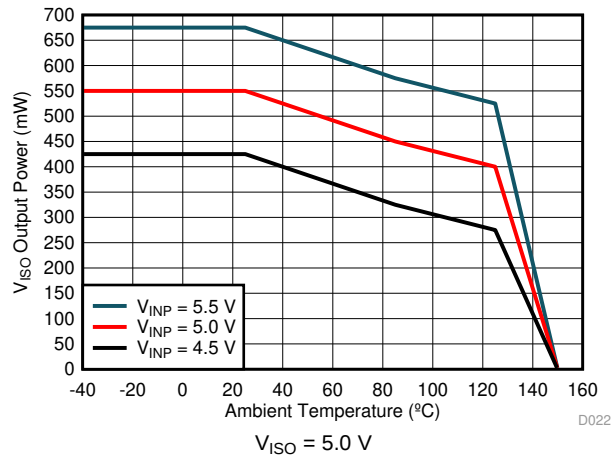


图 4. Maximum V_{ISO} Output Power vs. Temperature

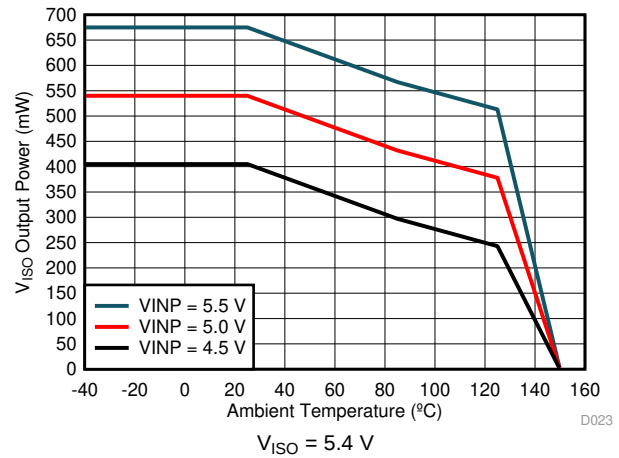


图 5. Maximum V_{ISO} Output Power vs. Temperature

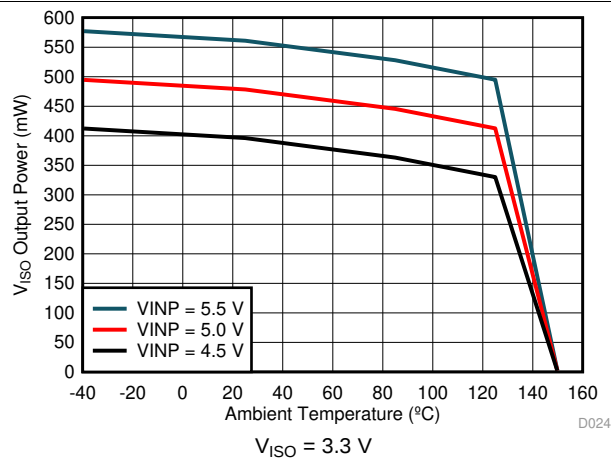


图 6. Maximum V_{ISO} Output Power vs. Temperature

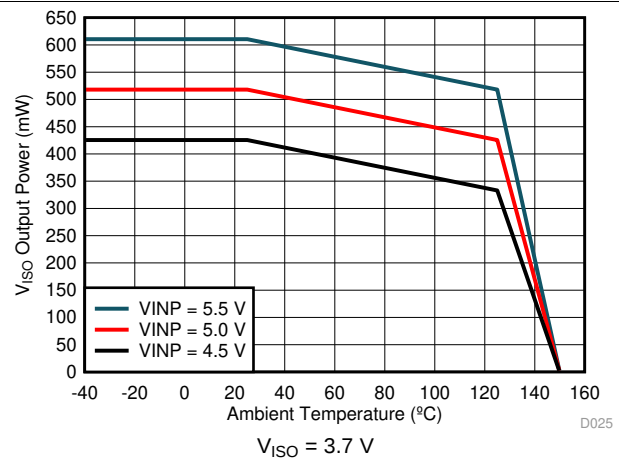


图 7. Maximum V_{ISO} Output Power vs. Temperature

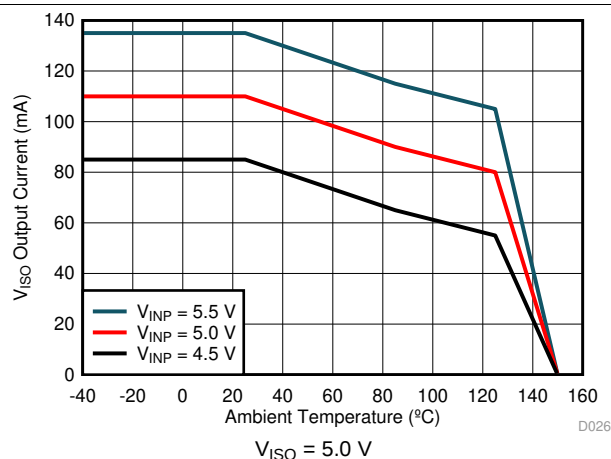


图 8. Maximum V_{ISO} Output Current vs. Temperature

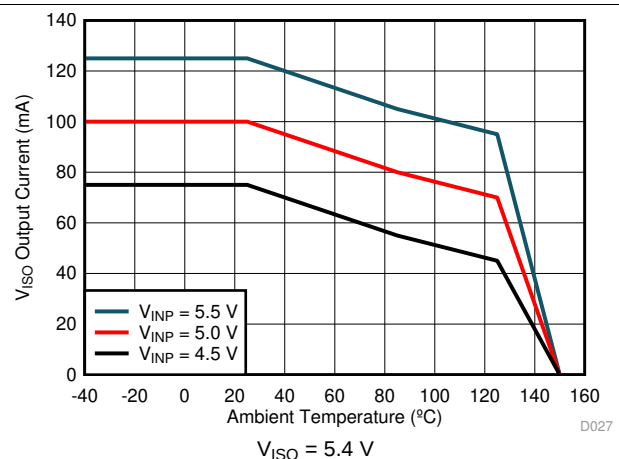


图 9. Maximum V_{ISO} Output Current vs. Temperature

Typical Characteristics (接下页)

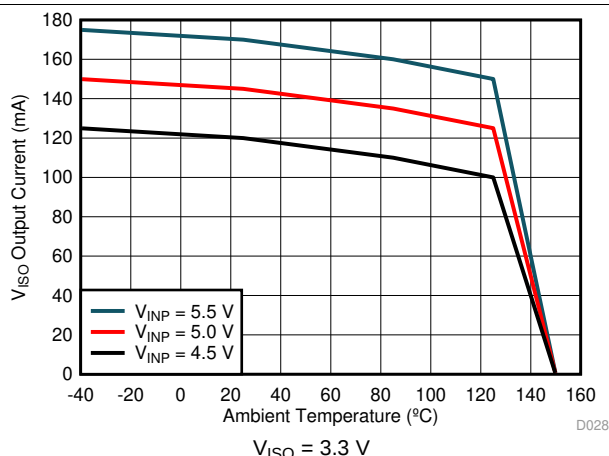


图 10. Maximum V_{ISO} Output Current vs. Temperature

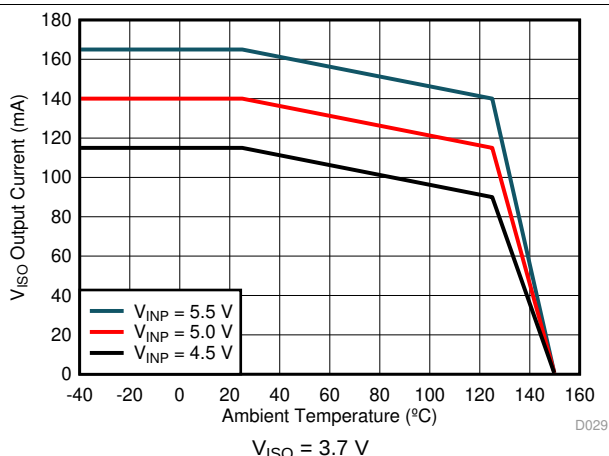


图 11. Maximum V_{ISO} Output Current vs. Temperature

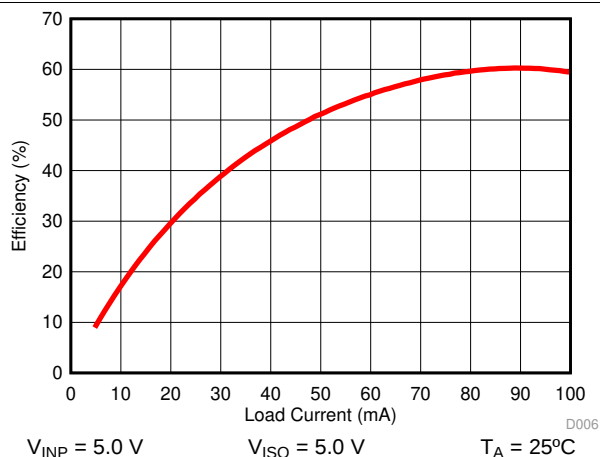


图 12. Power Supply Efficiency vs Load Current (I_{ISO})

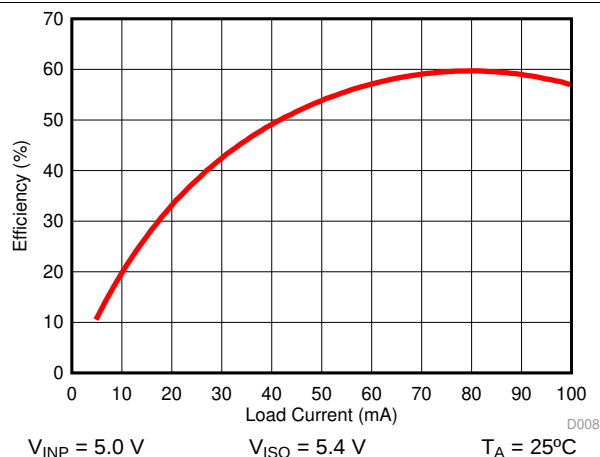


图 13. Power Supply Efficiency vs Load Current (I_{ISO})

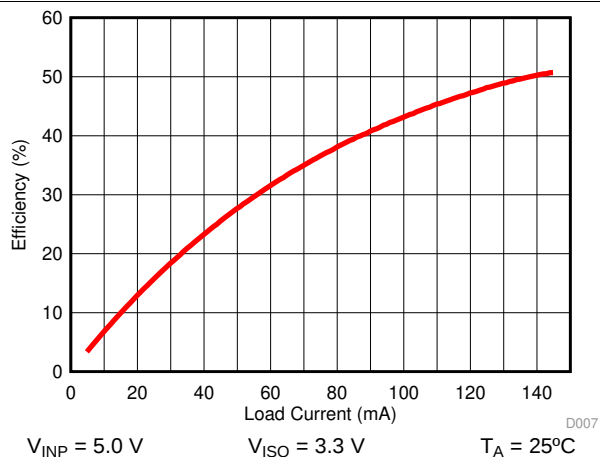


图 14. Power Supply Efficiency vs Load Current (I_{ISO})

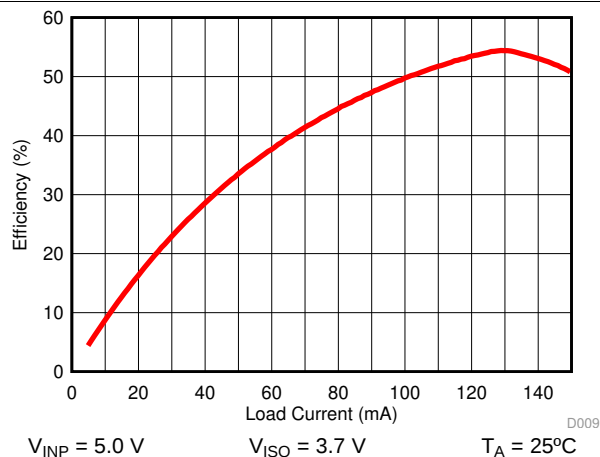


图 15. Power Supply Efficiency vs Load Current (I_{ISO})

Typical Characteristics (接下页)

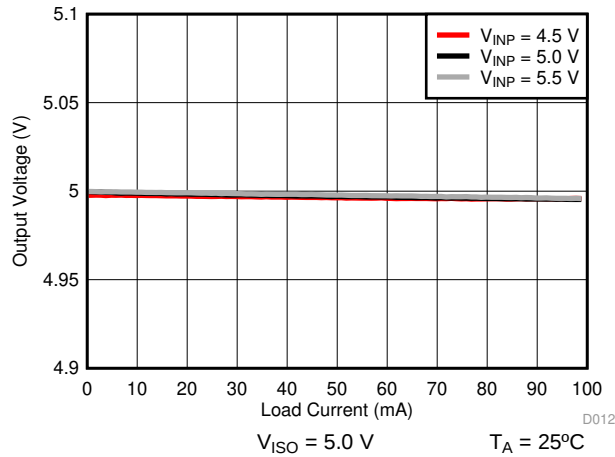


图 16. Isolated Supply Voltage (V_{ISO}) vs Load Current (I_{ISO})

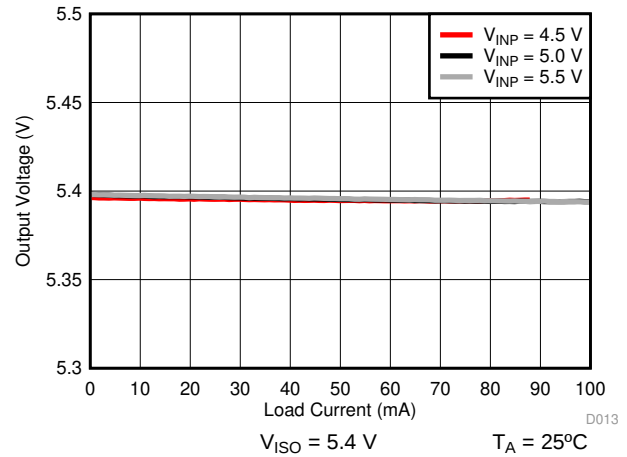


图 17. Isolated Supply Voltage (V_{ISO}) vs Load Current (I_{ISO})

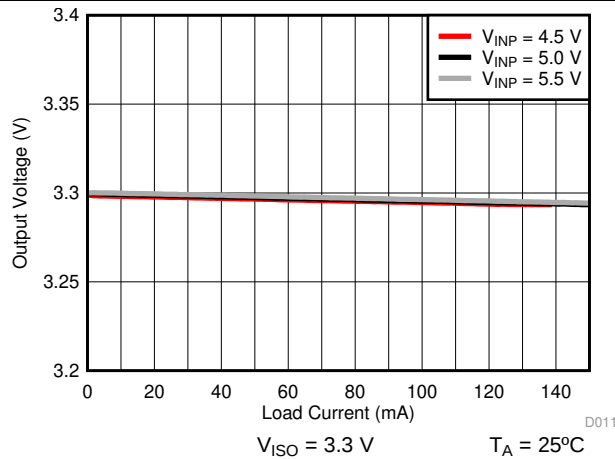


图 18. Isolated Supply Voltage (V_{ISO}) vs Load Current (I_{ISO})

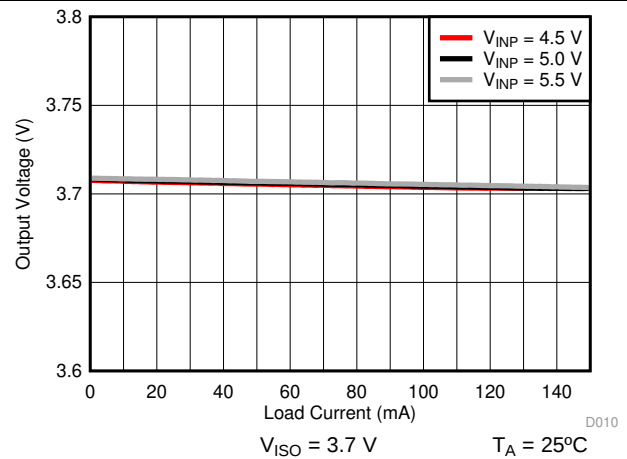


图 19. Isolated Supply Voltage (V_{ISO}) vs Load Current (I_{ISO})

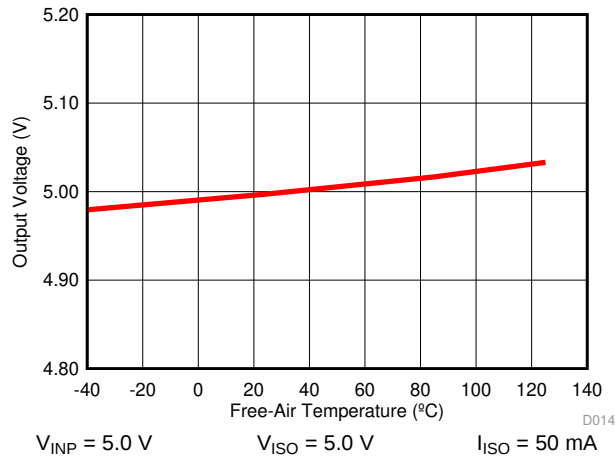


图 20. Isolated Supply Voltage (V_{ISO}) vs Free-Air Temperature

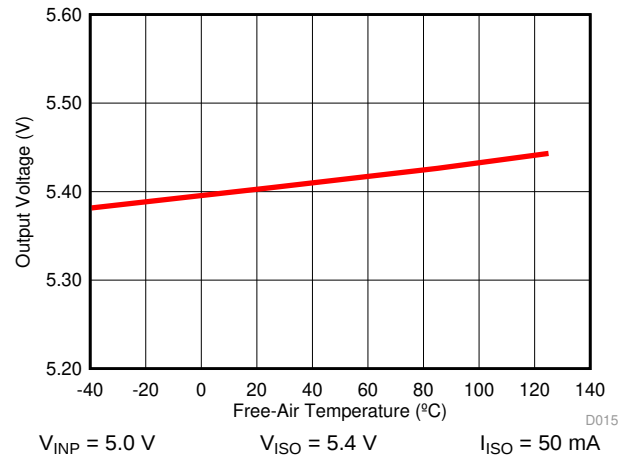


图 21. Isolated Supply Voltage (V_{ISO}) vs Free-Air Temperature

Typical Characteristics (接下页)

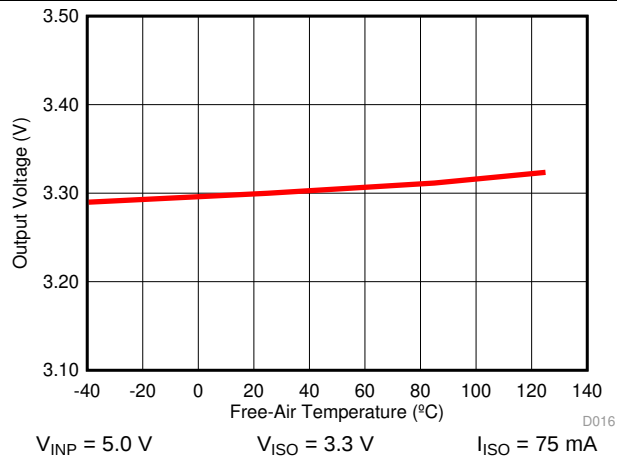


图 22. Isolated Supply Voltage (V_{ISO}) vs Free-Air Temperature

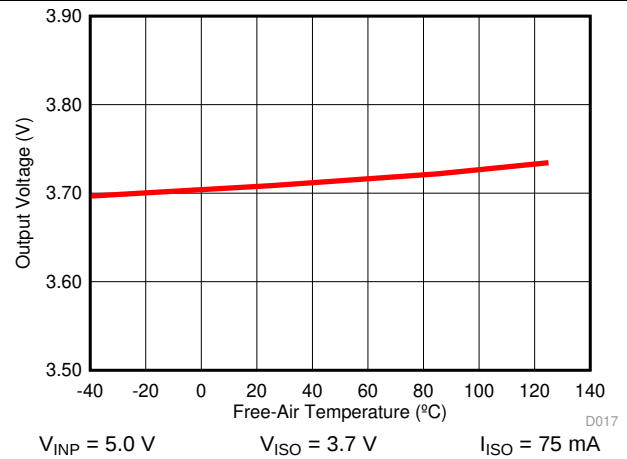


图 23. Isolated Supply Voltage (V_{ISO}) vs Free-Air Temperature

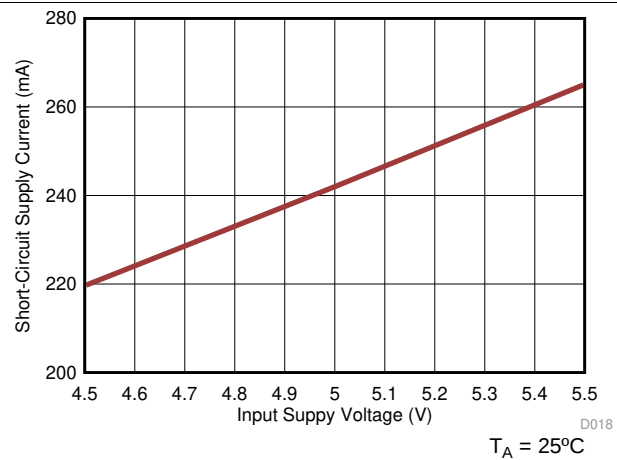


图 24. Short-Circuit Supply Current (I_{INP_SC}) vs Supply Voltage (V_{INP})

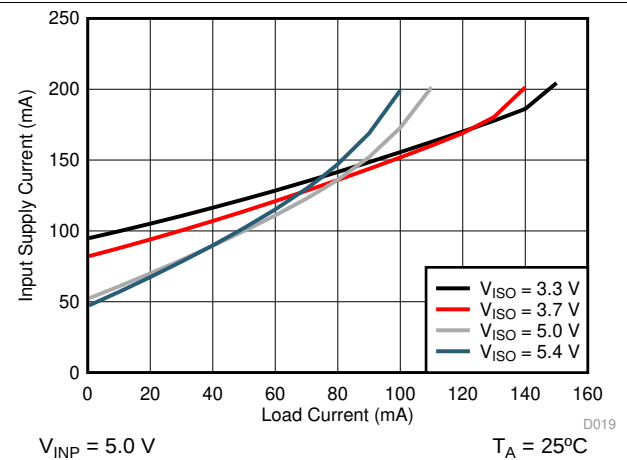


图 25. Input Supply Current (I_{INP}) vs Load Current (I_{ISO})

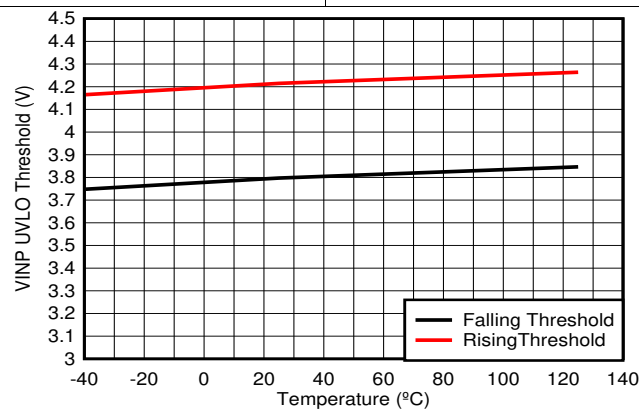


图 26. Typical V_{INP} UVLO Threshold vs Junction Temperature (T_J)

7 Detailed Description

7.1 Overview

The UCC12050 device integrates a high-efficiency, low-emissions isolated DC-DC converter. This approach provides typically 500 mW of clean, steady power across a 5000 V_{RMS} reinforced isolation barrier.

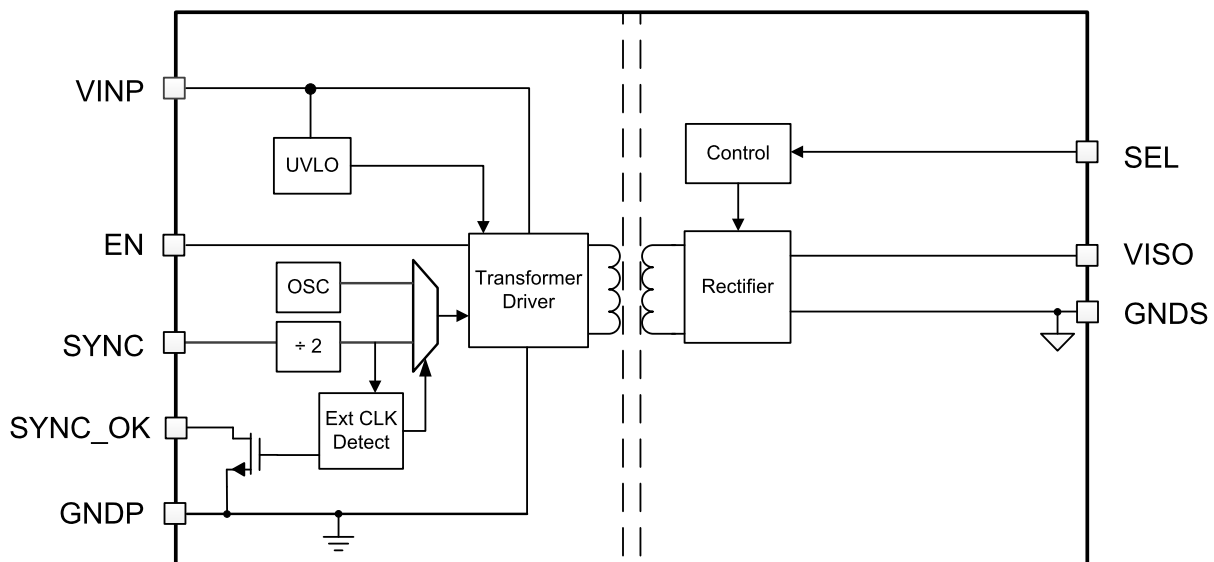
The integrated DC-DC converter uses switched mode operation and proprietary circuit techniques to reduce power losses and boost efficiency. Specialized control mechanisms, clocking schemes, and the use of an on-chip transformer provide high efficiency and low radiated emissions.

The VINP supply is provided to the primary power controller that switches the power stage connected to the integrated transformer. Power is transferred to the secondary side, rectified, and regulated to a level set by the SEL pin condition.

A fast feedback control loop monitors VISO and the output load, and ensures low overshoots and undershoots during load transients. Undervoltage lockout (UVLO) with hysteresis is integrated on the VINP supply, which ensures robust system performance under noisy conditions.

UCC12050 is suitable for applications that have limited board space and require more integration. These devices are also suitable for very-high voltage applications, where power transformers meeting the required isolation specifications are bulky and expensive.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Enable and Disable

Forcing EN low disables the device, which greatly reduces the VINP power consumption. Pull the EN pin high to enable normal device functionality. The EN pin has a weak internal pull-down resistor, so the device floats to the disable state if the pin is left open.

Feature Description (接下页)

7.3.2 UVLO, Power-Up, and Power-Down Behavior

The UCC12050 has an undervoltage lockout (UVLO) on the VINP power supply. Upon power-up, while the VINP voltage is below the threshold voltage V_{UVPR} , the primary side transformer driver is disabled, and VISO output is off. The output powers up once the threshold is met. Likewise, if VINP falls below V_{UVPF} , the converter is disabled and there is no output at VISO. Both UVLO threshold voltages have hysteresis to avoid chattering.

7.3.3 VISO Load Recommended Operating Area

图 27 depicts the device V_{ISO} regulation behavior across the output load range, including when the output is overloaded. For proper device operation, ensure that the device VISO output load does not exceed the maximum output current (I_{OUT_MAX}). The value for I_{OUT_MAX} over different temperature and V_{INP} conditions are shown from 图 8 to 图 11. The following protection mechanisms will be engaged if the UCC12050 is loaded beyond the recommended operating area:

1. The device limits the maximum output power. If a load exceeding I_{OUT_MAX} is applied, V_{ISO} drops accordingly to meet the maximum power limit.
2. If V_{ISO} drops below nominal 3.8 V while operating in the constant power limit region, the over-power fold-back feature will switch the power converter from active rectification to passive rectification, and the built-in recovery hysteresis will ensure the UCC12050 recovers at a lower output power. The device returns to active rectification when load drops and V_{ISO} increases above nominal 4.3V.
3. The device triggers a soft-start reset if V_{ISO} drops below the nominal 1.8-V threshold. This reset is designed to protect the device during V_{ISO} short-circuit conditions.
4. Thermal shutdown protection disables the converter if the device is operated in any of the above regions long enough to raise the silicon junction temperature above the thermal shutdown threshold. See the [Thermal Shutdown](#) section for more details on this device feature.

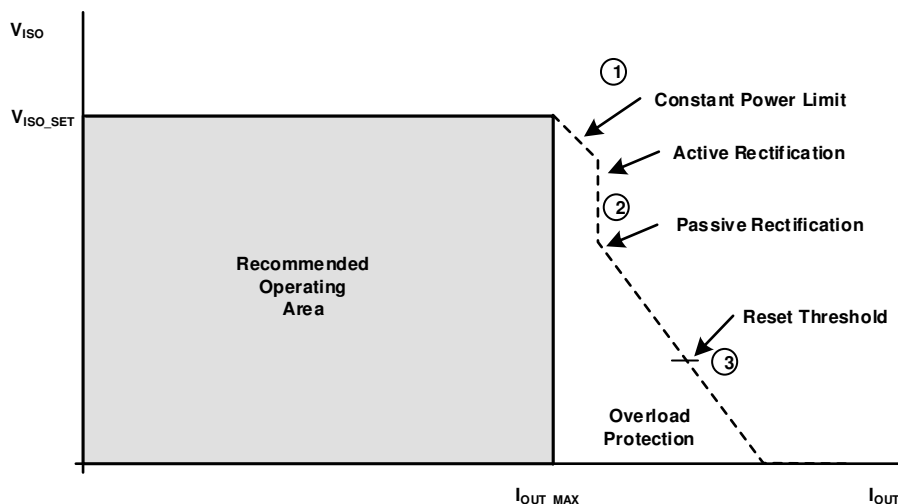


图 27. V_{ISO} Load Recommended Operating Area Description

7.3.4 Thermal Shutdown

Thermal protection is also integrated to help prevent the device from getting damaged during overload and short-circuit conditions on the isolated output. Under these conditions, the device temperature starts to increase. When the silicon junction temperature T_j sensed at the primary side die goes above the threshold TSD_{THR} (typical 165°C), thermal shutdown activates and the primary controller turns off which removes the energy supplied to the V_{ISO} load, which causes the device to cool off. When the junction temperature drops approximately 27°C (TSD_{HYST}) from the shutdown point, the device starts to function normally. If an overload or output short-circuit condition prevails, this protection cycle is repeated. Make sure the design prevents the device junction temperatures from reaching such high values.

Feature Description (接下页)

7.3.5 External Clocking and Synchronization

The UCC12050 has an internal oscillator trimmed to drive the transformer at 8.0 MHz. An external clock may be applied at the SYNC pin to override the internal oscillator. This external clock will be divided by 2, so the target range for the external clock signal at SYNC is 16 MHz $\pm$ 10%. The SYNC_OK pin is asserted LOW if there is no external SYNC clock or one that is outside of the operating range of the device is detected. In this state, the external clock is ignored and the DC-DC converter is clocked by the internal oscillator. The pin is in high-impedance if a good clock is applied on SYNC.

When more than one DC/DC converter is needed onboard, beat frequencies and other electrical interference can be generated. This interference occurs because of the small variations in switching frequencies between the DC/DC converters. The device overcomes this interference by allowing devices to synchronize to one another. Synchronize multiple devices by connecting the SYNC pins of each device, taking care to minimize the capacitance of all SYNC signal PCB traces. Stray capacitance (greater than 3 pF) may affect the switching frequency.

7.3.6 V_{ISO} Output Voltage Selection

The SEL pin is monitored during power-up — within the first 1 ms after applying VINP above the UVLO rising threshold or enabling via the EN pin — to detect the desired regulation voltage for the VISO output. Note that after this initial monitoring, the SEL pin no longer affects the VISO output level. In order to change the output mode selection, either the EN pin must be toggled or the VINP power supply must be cycled off and back on. Section 6.4 provides more details on the SEL pin functionality.

7.3.7 Electromagnetic Compatibility (EMC) Considerations

UCC12050 devices use emissions reduction schemes for the internal oscillator and advanced internal layout scheme to minimize radiated emissions at the system level.

Many applications in harsh industrial environment are sensitive to disturbances such as electrostatic discharge (ESD), electrical fast transient (EFT), surge and electromagnetic emissions. These electromagnetic disturbances are regulated by international standards such as IEC 61000-4-x and CISPR 32. Although system-level performance and reliability depends, to a large extent, on the application board design and layout, the device incorporates many chip-level design improvements for overall system robustness.

7.4 Device Functional Modes

表 2 lists the supply functional modes for this device.

表 2. Device Functional Modes

INPUTS		Isolated Supply Output Voltage (V_{ISO}) Setpoint
EN	SEL	
HIGH	Shorted to VISO	5.0 V
HIGH	100 k Ω to VISO	5.4 V
HIGH	Shorted to GNDS	3.3 V
HIGH	100 k Ω to GNDS	3.7 V
HIGH	OPEN ⁽¹⁾	UNSUPPORTED
LOW	X	0 V

(1) The SEL pin has an internal weak pull-down resistance to ground, but leaving this pin open is not recommended.

8 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The UCC12050 device is suitable for applications that have limited board space and desire more integration. This device is also suitable for very high voltage applications, where power transformers meeting the required isolation specifications are bulky and expensive.

8.2 Typical Application

图 28 shows the typical application schematic for the UCC12050 device supplying an isolated load.

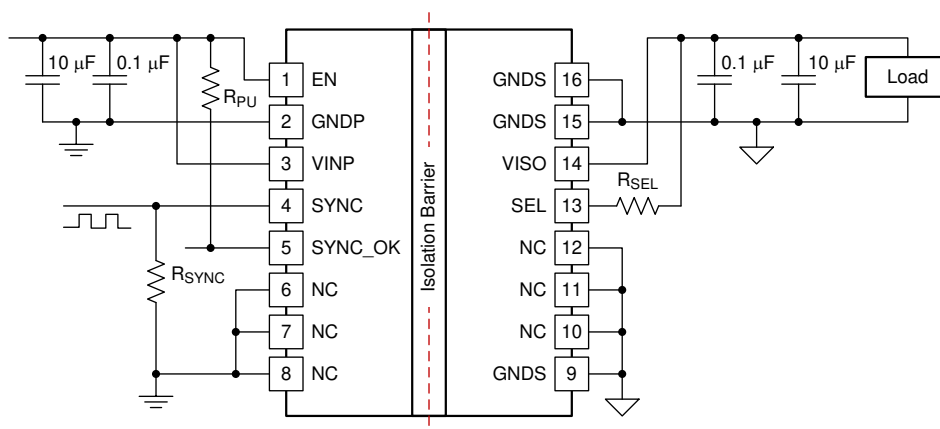


图 28. Typical Application

Typical Application (接下页)

8.2.1 Design Requirements

To design using UCC12050, a few simple design considerations must be evaluated. 表 3 shows some recommended values for a typical application. See [Power Supply Recommendations](#) and [Layout](#) sections to review other key design considerations for the UCC12050.

表 3. Design Parameters

PARAMETER	RECOMMENDED VALUE
Input supply voltage, V_{INP}	4.5 V to 5.5 V
Decoupling capacitance between V_{INP} and GNDP	10 μ F, 16 V, $\pm 10\%$, X7R
Decoupling capacitance between V_{ISO} and GNDS ⁽¹⁾	10 μ F, 16 V, $\pm 10\%$, X7R
Optional additional capacitance on V_{ISO} or V_{INP} to reduce high-frequency ripple	0.1 μ F, 50 V, $\pm 10\%$, X7R
Pull-up resistor from SYNC_OK to V_{INP} , R_{PU}	100 k Ω
Pull-up resistor from SEL to V_{ISO} for 5.0V output voltage mode, R_{SEL}	0 Ω
Pull-up resistor from SEL to V_{ISO} for 5.4V output voltage mode, R_{SEL}	100 k Ω
Optional SYNC signal impedance-matching resistor, R_{SYNC}	Match source — typical values are 50 Ω , 75 Ω , 100 Ω , or 1 k Ω
External clock signal applied on SYNC	16 MHz

(1) See [VISO Output Capacitor Selection](#) section.

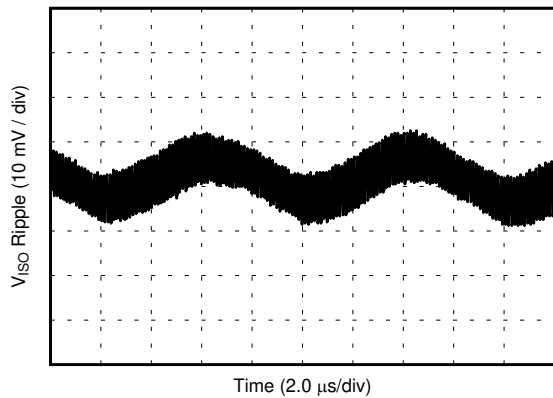
8.2.2 Detailed Design Procedure

Place ceramic decoupling capacitors as close as possible to the device pins. For the input supply, place the capacitor(s) between pin 3 (V_{INP}) and pin 2 (GNDP). For the isolated output supply, place the capacitor(s) between pin 14 (V_{ISO}) and pin 15 (GNDS). This location is of particular importance to the input decoupling capacitor, because this capacitor supplies the transient current associated with the fast switching waveforms of the power drive circuits. The recommended capacitor value is 10 μ F. Ensure the capacitor dielectric material is compatible with the target application temperature.

8.2.2.1 VISO Output Capacitor Selection

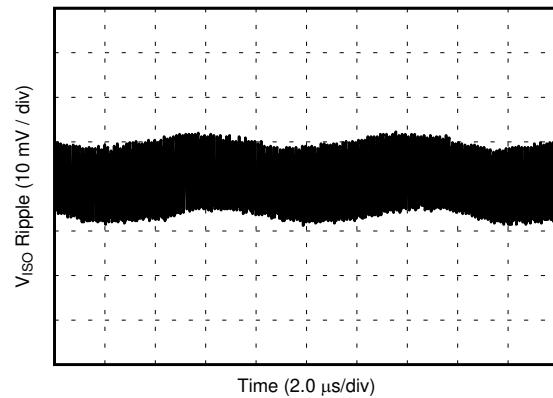
The UCC12050 is optimized to run with an effective output capacitance of 5 μ F to 20 μ F. A ceramic capacitor is recommended. Ceramic capacitors have DC-Bias and temperature derating effects, which both have influence the final effective capacitance. Choose the right capacitor carefully in combination with considering its package size, dielectric and voltage rating. It is good design practice to include one 0.1- μ F capacitor close to the device for high-frequency noise reduction.

8.2.3 Application Curves



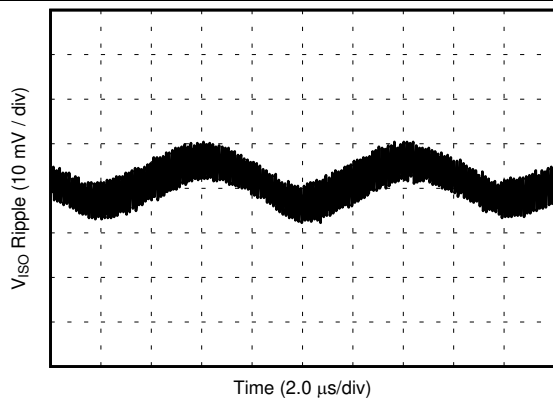
V_{INP} = 5.0 V V_{ISO} = 5.4 V Bandwidth = 20 MHz D033

图 29. V_{ISO} Ripple, 5.4-V Output, 10% Load



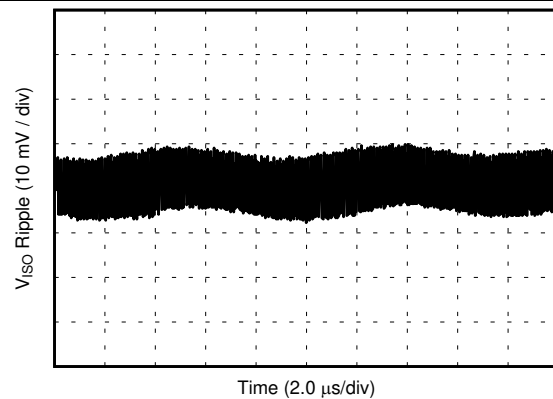
V_{INP} = 5.0 V V_{ISO} = 5.4 V Bandwidth = 20 MHz D034

图 30. V_{ISO} Ripple, 5.4-V Output, 90% Load



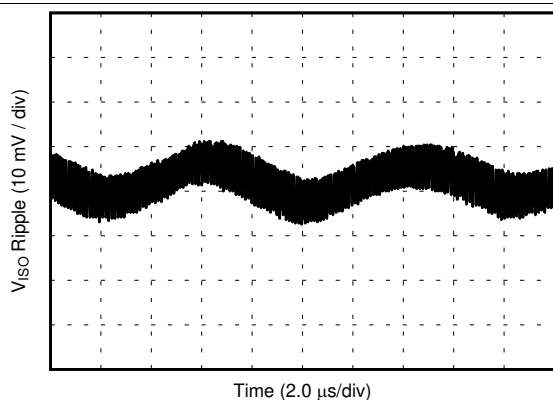
V_{INP} = 5.0 V V_{ISO} = 5.0 V Bandwidth = 20 MHz D035

图 31. V_{ISO} Ripple, 5.0-V Output, 10% Load



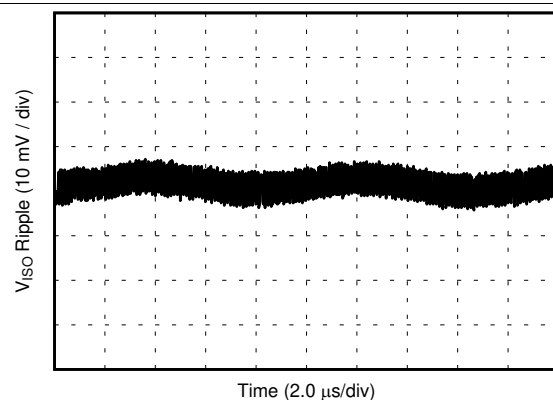
V_{INP} = 5.0 V V_{ISO} = 5.0 V Bandwidth = 20 MHz D036

图 32. V_{ISO} Ripple, 5.0-V Output, 90% Load



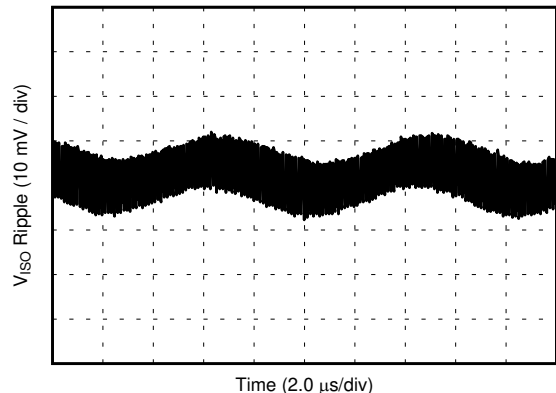
V_{INP} = 5.0 V V_{ISO} = 3.7 V Bandwidth = 20 MHz D037

图 33. V_{ISO} Ripple, 3.7-V Output, 10% Load



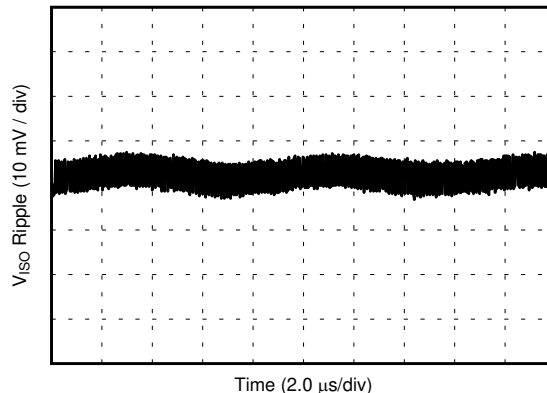
V_{INP} = 5.0 V V_{ISO} = 3.7 V Bandwidth = 20 MHz D038

图 34. V_{ISO} Ripple, 3.7-V Output, 90% Load



$V_{INP} = 5.0\text{ V}$ $V_{ISO} = 3.3\text{ V}$ Bandwidth = 20 MHz D039

图 35. V_{ISO} Ripple, 3.3-V Output, 10% Load



$V_{INP} = 5.0\text{ V}$ $V_{ISO} = 3.3\text{ V}$ Bandwidth = 20 MHz D040

图 36. V_{ISO} Ripple, 3.3-V Output, 90% Load

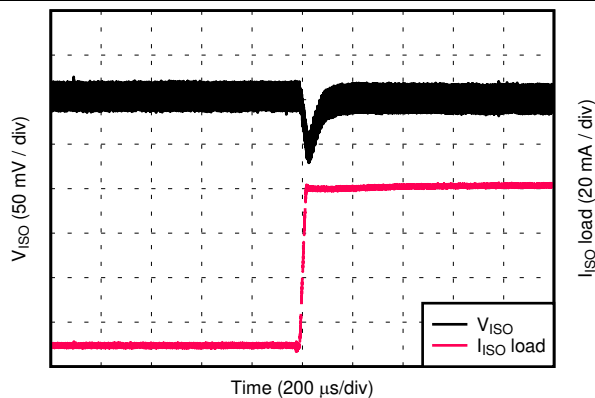


图 37. V_{ISO} Load Transient Response, 10% to 90% Load Step, 5.0-V Input, 5.4-V Output D041

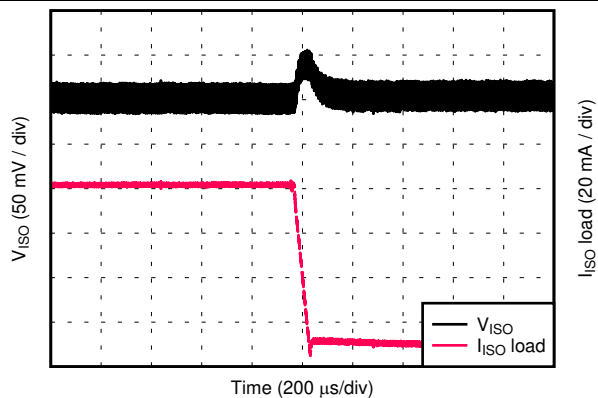


图 38. V_{ISO} Load Transient Response, 90% to 10% Load Step, 5.0-V Input, 5.4-V Output D042

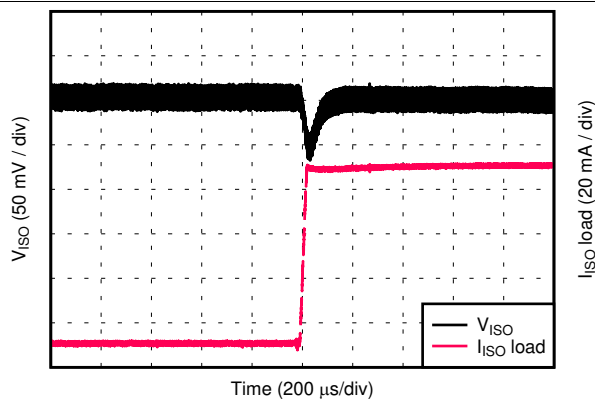


图 39. V_{ISO} Load Transient Response, 10% to 90% Load Step, 5.0-V Input, 5.0-V Output D043

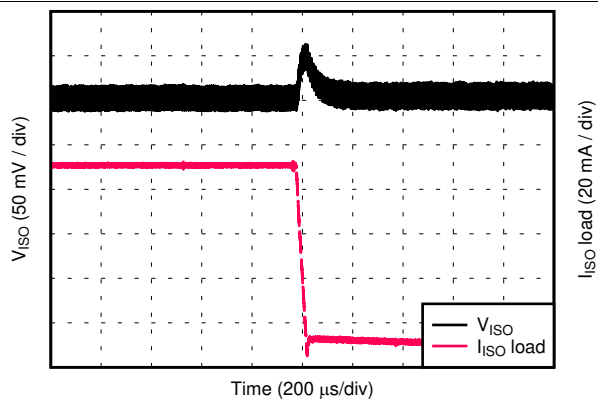


图 40. V_{ISO} Load Transient Response, 90% to 10% Load Step, 5.0-V Input, 5.0-V Output D044

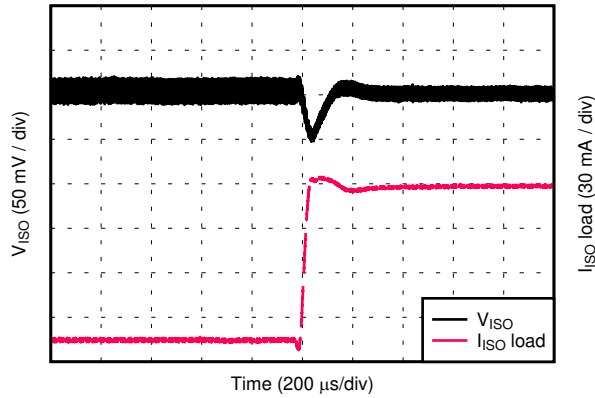


图 41. V_{ISO} Load Transient Response, 10% to 90% Load Step, 5.0-V Input, 3.7-V Output

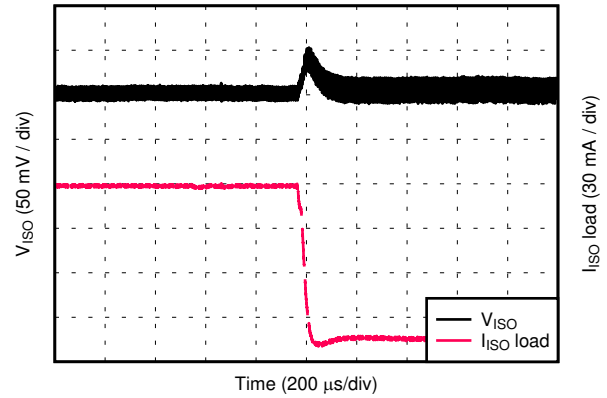


图 42. V_{ISO} Load Transient Response, 90% to 10% Load Step, 5.0-V Input, 3.7-V Output

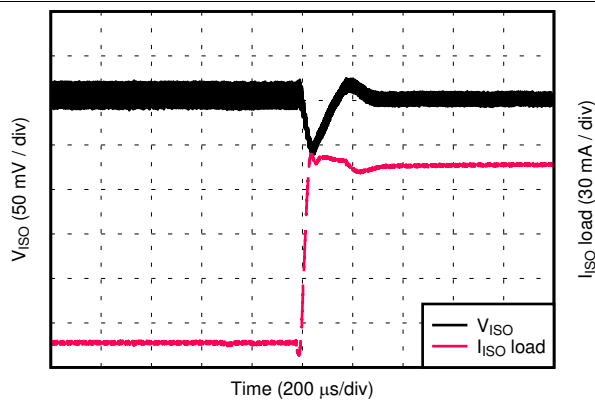


图 43. V_{ISO} Load Transient Response, 10% to 90% Load Step, 5.0-V Input, 3.3-V Output

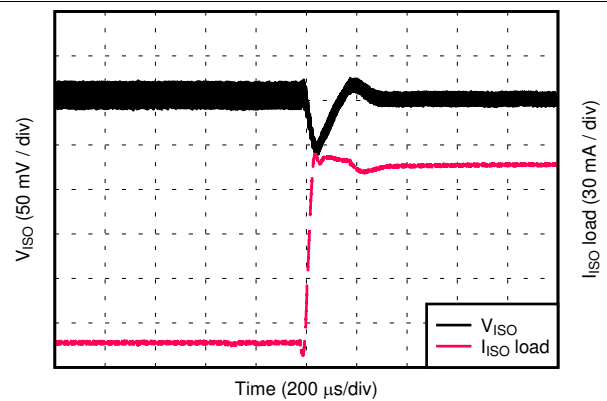


图 44. V_{ISO} Load Transient Response, 90% to 10% Load Step, 5.0-V Input, 3.3-V Output

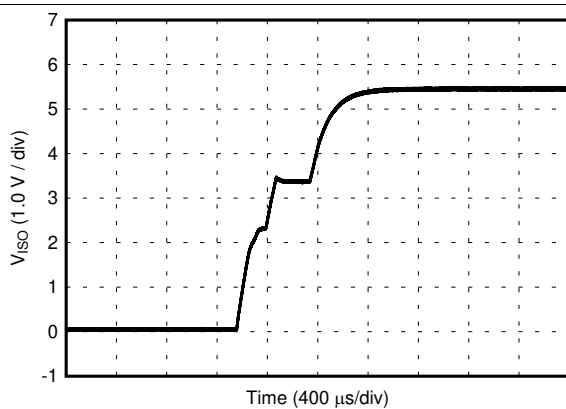


图 45. V_{ISO} Soft Start at 10% Rated Load, 5.0-V Input, 5.4-V Output

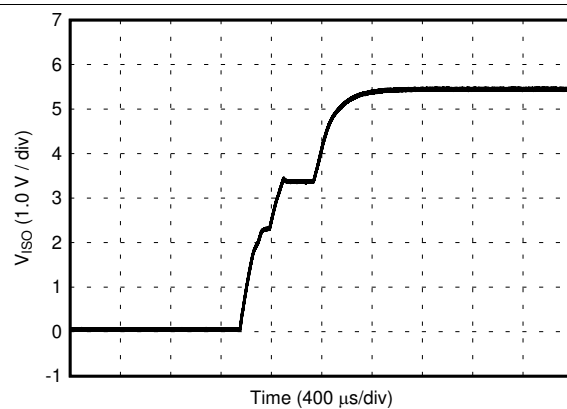


图 46. V_{ISO} Soft Start at 90% Rated Load, 5.0-V Input, 5.4-V Output

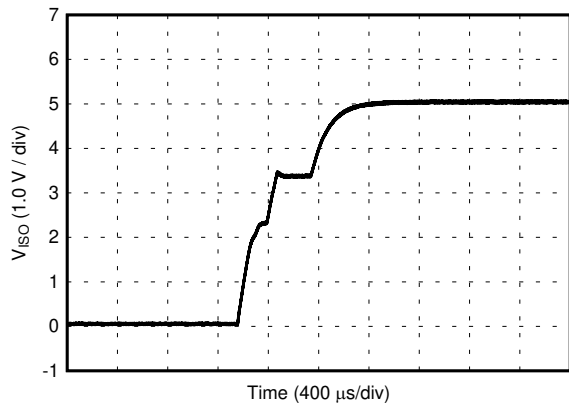


图 47. V_{ISO} Soft Start at 10% Rated Load, 5.0-V Input, 5.0-V Output

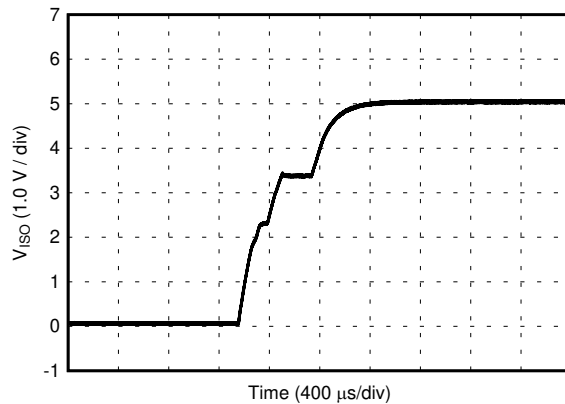


图 48. V_{ISO} Soft Start at 90% Rated Load, 5.0-V Input, 5.0-V Output

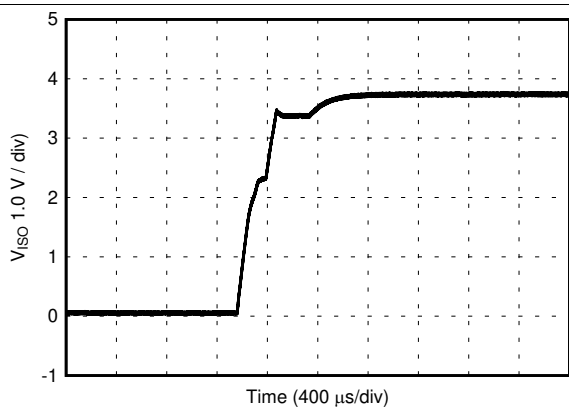


图 49. V_{ISO} Soft Start at 10% Rated Load, 5.0-V Input, 3.7-V Output

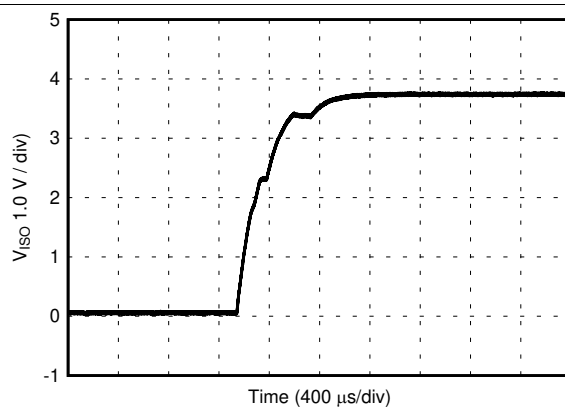


图 50. V_{ISO} Soft Start at 90% Rated Load, 5.0-V Input, 3.7-V Output

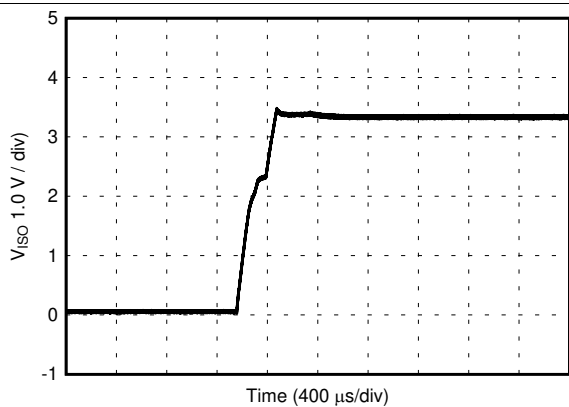


图 51. V_{ISO} Soft Start at 10% Rated Load, 5.0-V Input, 3.3-V Output

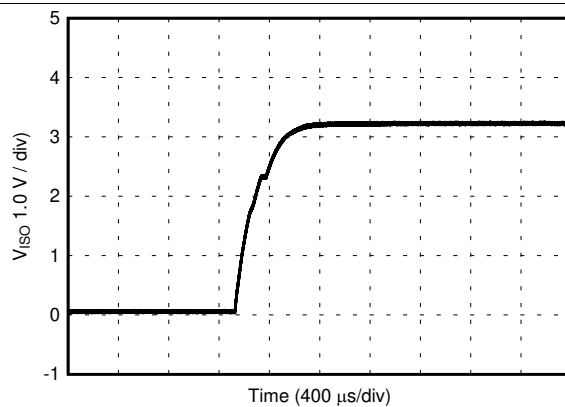


图 52. V_{ISO} Soft Start at 90% Rated Load, 5.0-V Input, 3.3-V Output

9 Power Supply Recommendations

The recommended input supply voltage (VINP) for the UCC12050 is between 4.5 V and 5.5 V. To help ensure reliable operation, adequate decoupling capacitors must be located as close to supply pins as possible. Place local bypass capacitors between the VINP and GNDP pins at the input, and between VISO and GNDS at the isolated output supply. Low ESR, ceramic surface mount capacitors are recommended. It is further suggested that one place two such capacitors: one with a value of 10 μ F for supply bypassing, and an additional 100-nF capacitor in parallel for high frequency filtering. The input supply must have an appropriate current rating to support output load required by the end application.

10 Layout

10.1 Layout Guidelines

The UCC12050 integrated isolated power solution simplifies system design and reduces board area usage. Proper PCB layout is important in order to achieve optimum performance. Here is a list of recommendations:

1. Place decoupling capacitors as close as possible to the device pins. For the input supply, place the capacitor(s) between pin 3 (VINP) and pin 2 (GNDP). For the isolated output supply, place the capacitor(s) between pin 14 (VISO) and pin 15 (GNDS). This location is of particular importance to the input decoupling capacitor, because this capacitor supplies the transient current associated with the fast switching waveforms of the power drive circuits.
2. Because the device does not have a thermal pad for heat-sinking, the device dissipates heat through the respective GND pins. Ensure that enough copper (preferably a connection to the ground plane) is present on all GNDP and GNDS pins for best heat-sinking.
3. If space and layer count allow, it is also recommended to connect the VINP, GNDP, VISO and GNDS pins to internal ground or power planes through multiple vias of adequate size. Alternatively, make traces for these nets as wide as possible to minimize losses.
4. TI also recommends grounding the no-connect pins (NC) to their respective ground planes. For pins 6, 7, and 8, connect to GNDP. For pins 10, 11, and 12, connect to GNDS. This will allow more continuous ground planes and larger thermal mass for heat-sinking.
5. A minimum of four layers is recommended to accomplish a low-EMI PCB design. Inner layers can be spaced closer than outer layers and used to create a high-frequency bypass capacitor between GNDP and GNDS to reduce radiated emissions. Ensure proper spacing, both inter-layer and layer-to-layer, is implemented to avoid reducing isolation capabilities. These spacings will vary based on the printed circuit board construction parameters, such as dielectric material and thickness.
6. Pay close attention to the spacing between primary ground plane (GNDP) and secondary ground plane (GNDS) on the PCB outer layers. The effective creepage and or clearance of the system will be reduced if the two ground planes have a lower spacing than that of the device package.
7. To ensure isolation performance between the primary and secondary side, avoid placing any PCB traces or copper below the UCC12050 device on the outer copper layers.

10.2 Layout Example

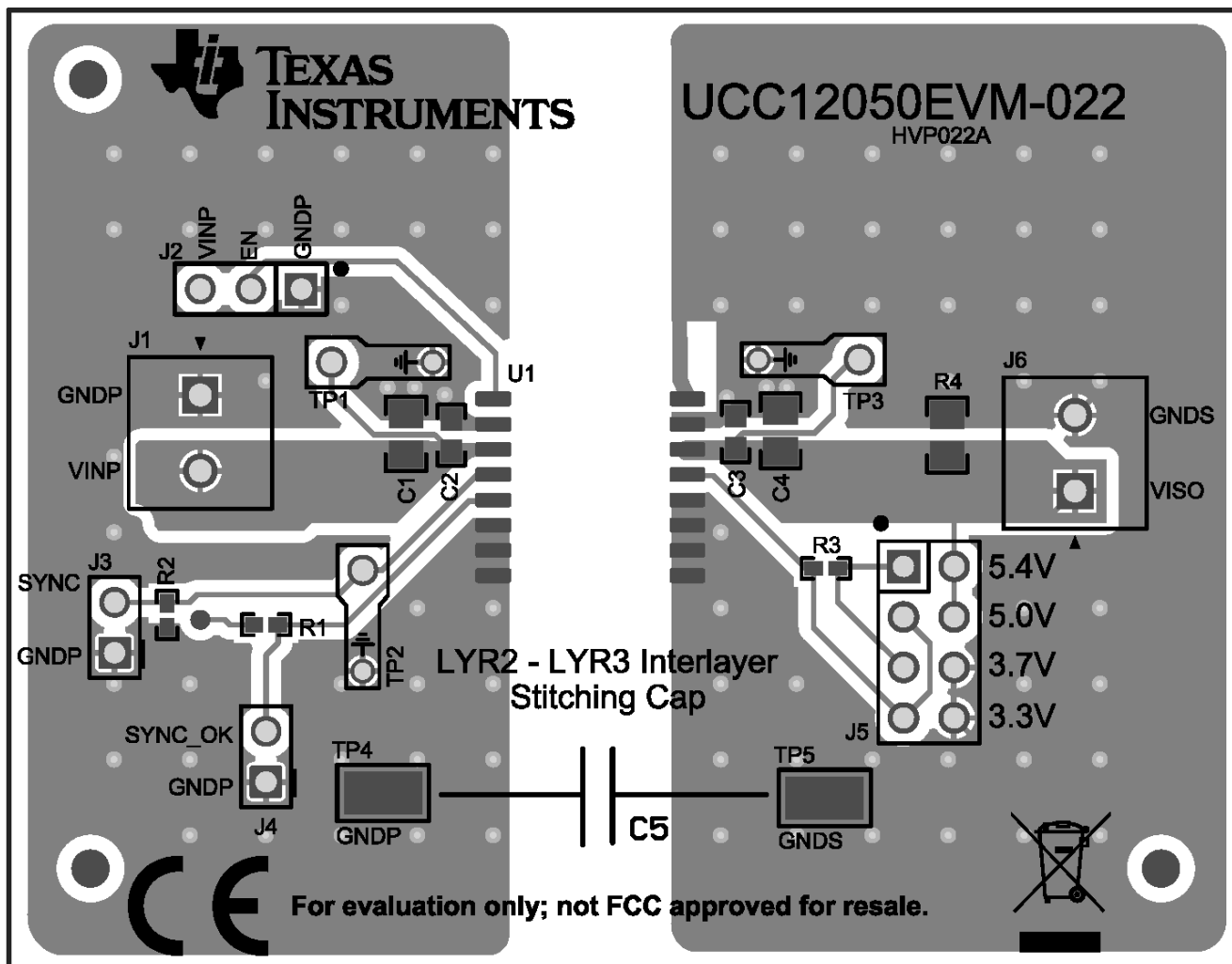


图 53. Layout Example

11 器件和文档支持

11.1 器件支持

11.1.1 开发支持

有关开发支持，请参阅：

- [基于高效、低辐射、隔离式直流/直流转换器的模拟输入模块参考设计](#)
- [基于隔离式 \$\Delta\$ - \$\Sigma\$ 调制器的交流/直流电压和电流测量模块参考设计](#)
- [适用于通信和模拟输入/输出模块的隔离式电源架构参考设计](#)

11.2 文档支持

11.2.1 相关文档

请参阅如下相关文档：

- [《UCC12050 评估模块用户指南》](#)
- [《隔离相关术语》](#)
- [《适用于空间受限应用的增强隔离模拟 输入链》](#)

11.3 接收文档更新通知

要接收文档更新通知，请导航至 TI.com.cn 上的器件产品文件夹。单击右上角的通知我 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

11.4 社区资源

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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11.5 商标

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11.6 静电放电警告



ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

11.7 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 机械和封装信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
UCC12050DVE	ACTIVE	SO-MOD	DVE	16	40	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	UCC12050	Samples
UCC12050DVER	ACTIVE	SO-MOD	DVE	16	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	UCC12050	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

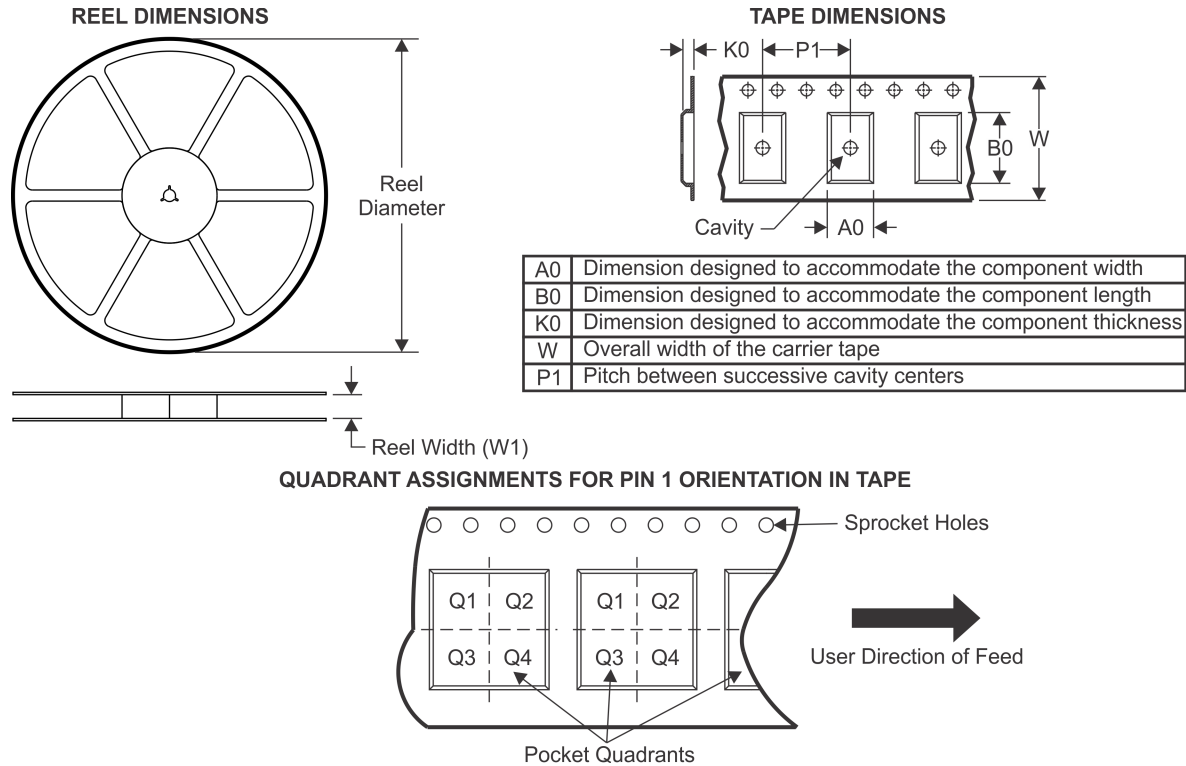
(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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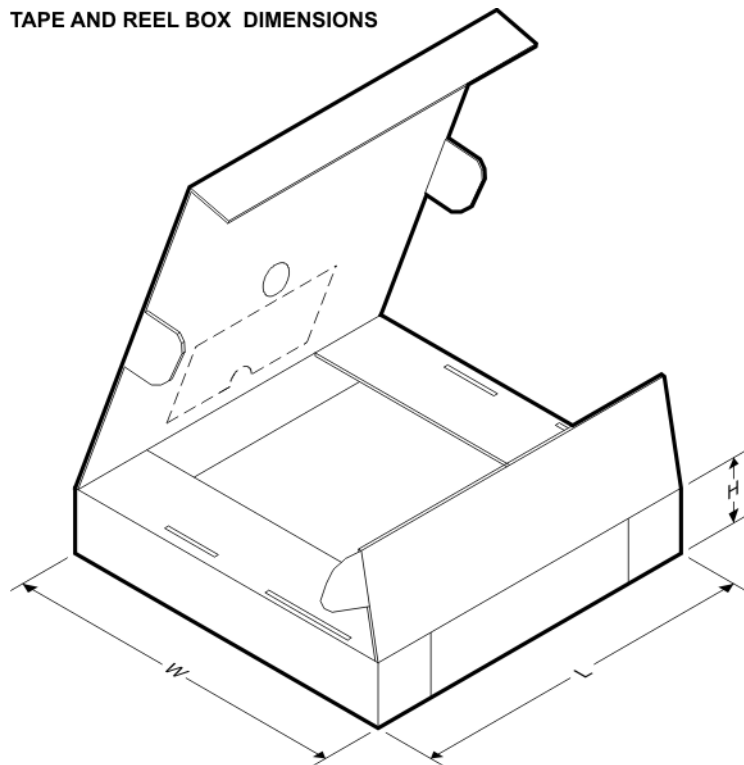
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
UCC12050DVER	SO-MOD	DVE	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1

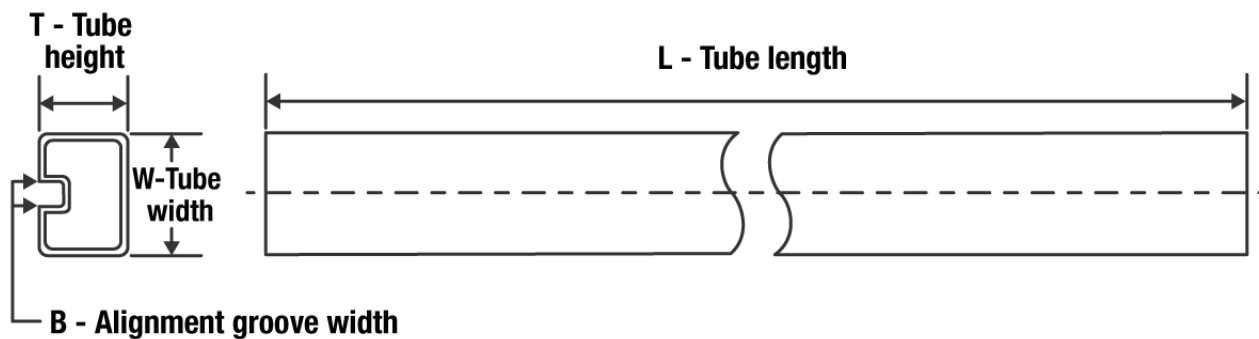
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

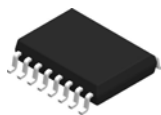
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
UCC12050DVER	SO-MOD	DVE	16	2000	350.0	350.0	43.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
UCC12050DVE	DVE	SO-MOD	16	40	506.98	12.7	4826	6.6

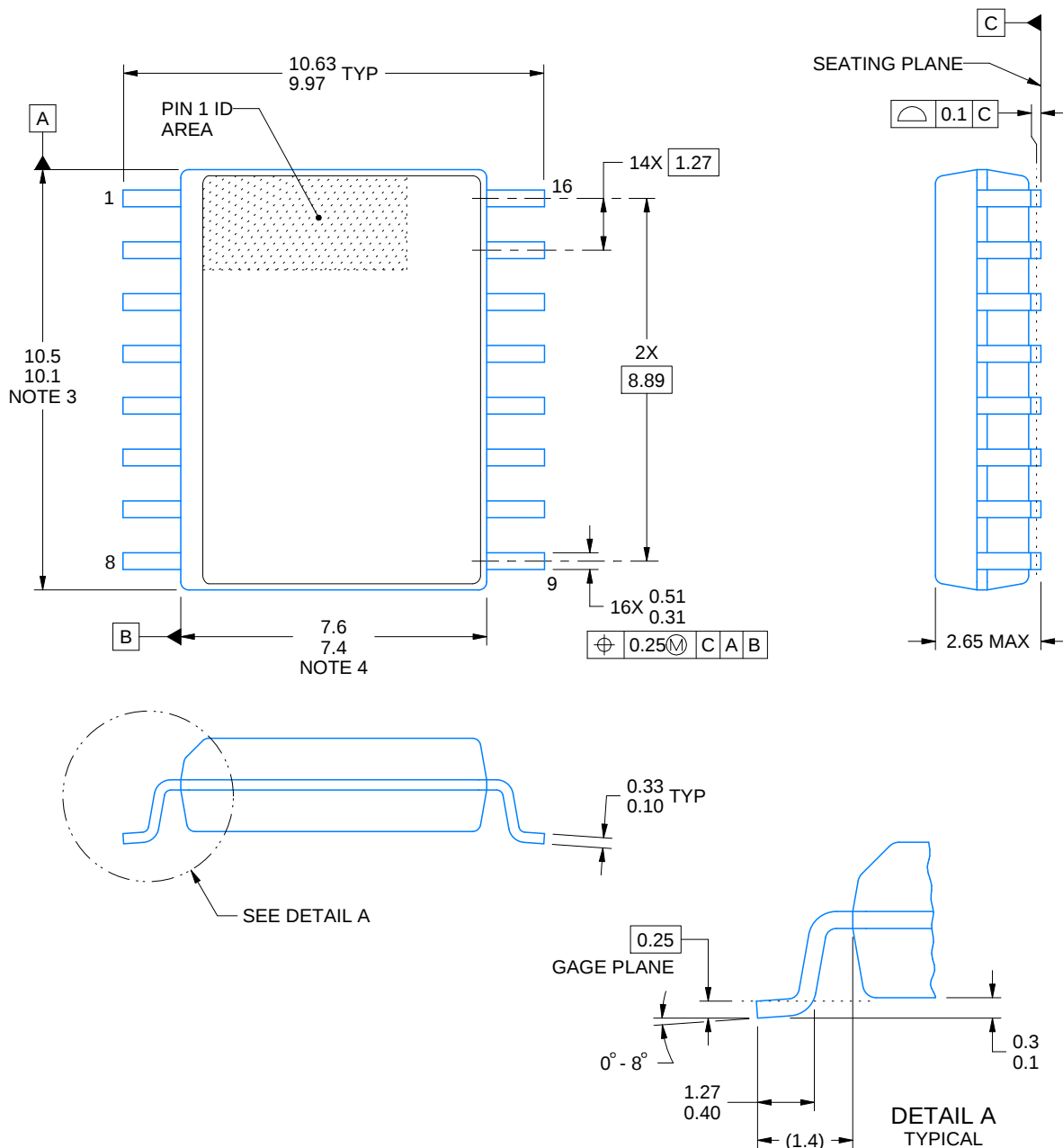


DVE0016A

PACKAGE OUTLINE

SO-MOD - 2.65 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4224275/A 04/2018

NOTES:

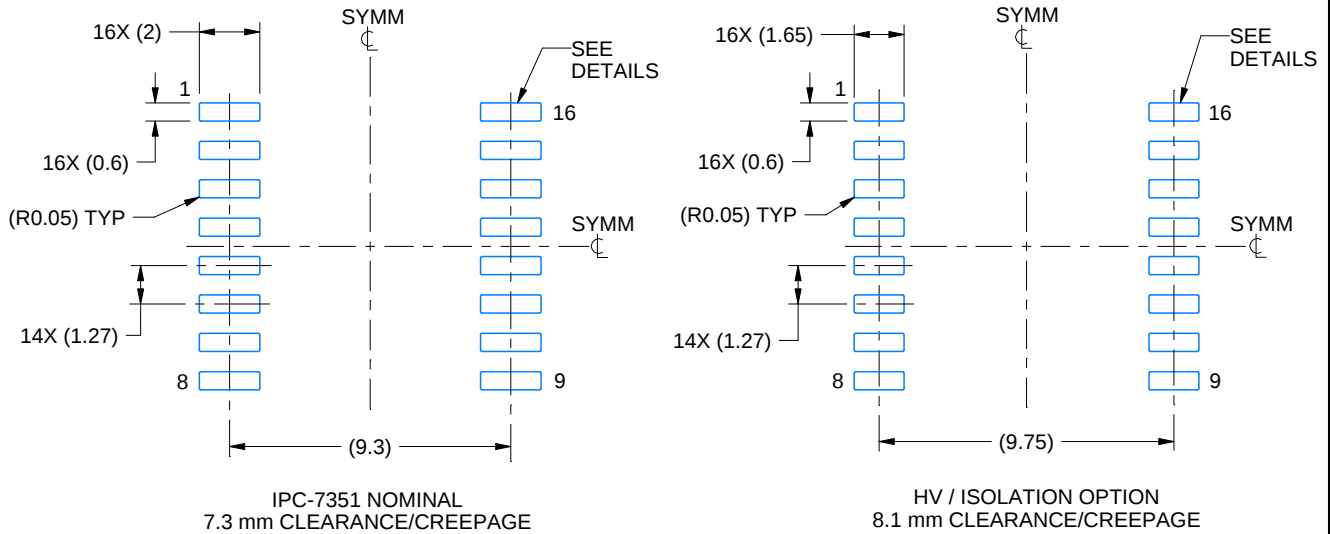
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
5. Reference JEDEC registration MS-013.

EXAMPLE BOARD LAYOUT

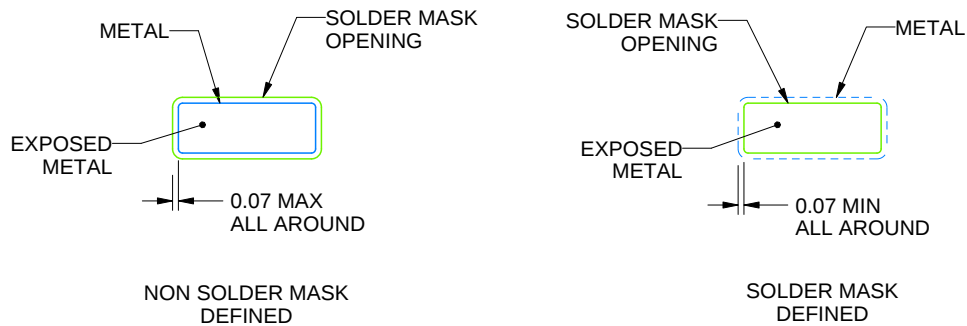
DVE0016A

SO-MOD - 2.65 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:4X



SOLDER MASK DETAILS

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NOTES: (continued)

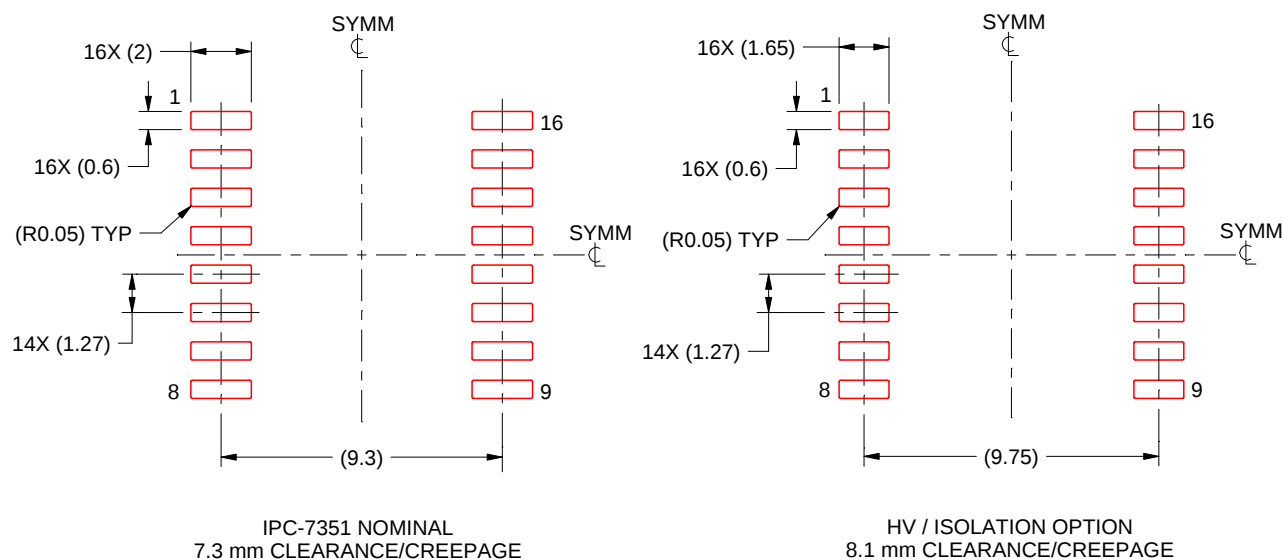
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DVE0016A

SO-MOD - 2.65 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:4X

4224275/A 04/2018

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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